

MASTR Progress Line

25-50 MHz RECEIVER MODELS 4ER39C28-45



SPECIFICATIONS

FCC Filing Designation

Frequency Range

Audio Output

Sensitivity

12-dB SINAD (EIA Method) 20-dB Quieting Method

Selectivity

EIA Two-Signal Method 20-dB Quieting Method

Spurious Response

First Oscillator Stability

Modulation Acceptance

Squelch Sensitivity

Critical Squelch Maximum Squelch

Intermodulation (EIA)

Maximum Frequency Separation

Frequency Response

ER-39-C

25-50 MHz

5 watts at less than 5% distortion

 $0.25 \mu V$ 0.35 μV

-85 dB (adjacent channel, 20 kHz channels) -100 dB at ± 15 kHz

-100 dB

 $\pm .0005\%$ (-30°C to +60°C)

±7 kHz (narrow-band)

0.15 μV Greater than 20 dB quieting (less than $1.5 \mu V$

-60 dB

0.4%

+1 and -8 dB of a standard 6-dB per octave de-emphasis curve from 300 to 3000 Hz (1000-Hz reference)

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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— WARNING —

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power.

KEEP AWAY FROM LIVE CIRCUITS

DESCRIPTION

General Electric MASTR Progress Line Receiver Type ER-39-C is a double conversion, superheterodyne FM receiver designed for operation on the 25-50 megahertz band.

The receiver is of single-unit construction and is completely housed in a copper-plated aluminum casting for maximum shielding and rigidity. The top compartment of the casting contains the RF, oscillator, converter, and 1st low IF amplifier, and noise blanker. The bottom portion of the casting contains the audio-squelch board and the optional Channel Guard board.

CIRCUIT ANALYSIS

The MASTR Progress Line Receiver is completely transistorized, using silicon transistors throughout for added reliability. Input leads to the receiver are individually filtered by the 20-pin feed-through by-pass connector J443. A regulated +10 volts is used for all receiver stages except the audio PA stage which operates from the 12-volt system supply.

Centralized metering jack J442 is provided for use with General Electric Test Set Model 4EX3A10 or 4EX8K10, 11 for ease of alignment and servicing. The Test Set meters the noise blanker, multiplier, and limiter stages as well as the discriminator, and regulated 10 volts.

RF AMPLIFIERS (A341 & A344)

lst RF Amplifier (A341) consists of two high-Q helical resonators and an RF amplifier stage (Q1). The RF signal from the antenna is coupled by RF cable W441 to a tap on L341/L343/L345. The tap is positioned to insure the proper impedance match to the antenna. RF energy is coupled through the two coils by an opening in the shield wall to the base of 1st RF Amplifier Q1. The coils are tuned to the incoming frequency by air trimmer capacitors C341 and C342.

The output of Ql is coupled through two or four tuned circuits to the base of the 2nd RF Amplifier (A344-Ql).

The output of the 2nd RF Amplifier (A344) is coupled through three tuned circuits to the base of 1st Mixer A369-Q2.

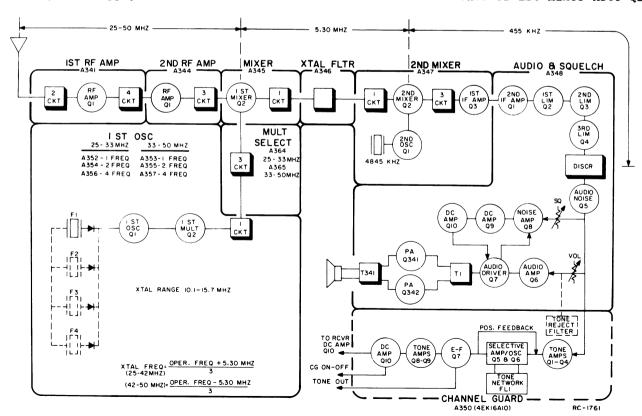


Figure 1 - Receiver Block Diagram

1ST OSCILLATOR AND MULTIPLIER (A352-A357)

The receiver 1st oscillator operates in a transistorized Colpitts oscillator circuit. The oscillator crystal operates in a fundamental mode at a frequency of approximately 10 to 15 megahertz. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides ±.0005% frequency stability as soon as the receiver is energized — without the warm-up time required by crystal ovens or warmers.

In single frequency receivers, bias for the oscillator is obtained by a jumper from H1 to H2 on the oscillator board.

In multi-frequency receivers, a diode is connected in series with the crystal, and up to three additional crystal circuits can be added. The 10-volt jumper is removed and the proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit.

Switching the +10 volts to the crystal circuit forward biases the diode and reduces its impedance. This applies the crystal frequency to the base of oscillator transistor Ql. Feedback for the oscillator is developed across C21/C22. The output is coupled to the base of 1st multiplier Q2.

The output of the 1st multiplier (tripler Q2) is transformer-coupled (T3/T4) to multiplier selectivity assembly A364/A365. The multiplier tank is tuned to three times the crystal frequency. The stage is metered at centralized metering jack J442-4 through metering network CR1, R1, C5 and C6.

MULTIPLIER SELECTIVITY ASSEMBLY (A364/A365)

Following the 1st multiplier tank (T3/T4) are two additional L-C tuned circuits (A364/A365-L1, L2 and L3. Capacitor C12/C16 couples the multiplier selectivity output to the base of the first mixer.

1ST MIXER (A369) AND CRYSTAL FILTER (A346)

The RF signal from the RF amplifier and the injection voltage from the 1st multiplier are applied to the base of 1st mixer A345-Q2. The mixer collector tank (L2 and C3) is tuned to 5.3 megahertz and provides impedance matching to the high IF crystal filter.

A highly selective crystal filter (A346) following the 1st mixer provides the major selectivity for the receiver. The output of the filter is fed through impedance matching transformer A347-T1 to the base of the 2nd mixer.

2ND OSCILLATOR, 2ND MIXER AND 1ST LO IF AMPLIFIER (A347)

A347-Q2 operates in a Colpitts oscillator circuit, with feedback supplied through C4. The oscillator low-side injection voltage (4845 kHz) is applied to the base of the 2nd mixer.

The High IF signal from the filter and the injection voltage from the 2nd oscillator is applied to the base of 2nd mixer Q2. The 455 kHz mixer output is applied to three tuned low IF circuits, L1, L2 and L3. These tuned circuits are required for shaping the nose of the IF waveform, and for rejecting any undesired output frequencies from the 2nd mixer.

The low IF signal is applied to the base of 1st low IF amplifier A347-Q3. The output of A347-Q3 is R-C coupled to the base of the 2nd low IF amplifier.

2ND LO IF AMPLIFIER AND LIMITERS (A348)

Additional amplification of the low IF signal going to the limiter stages is provided by 2nd low IF amplifier A318-Q1. This stage is metered at J442-2 through a metering network consisting of C19, CR3 and R25.

Following the 2nd low IF amplifier are three R-C coupled limiter stages (A348-Q2, Q3 and Q4). The 1st limiter is metered at J442-3 through metering network C20, CR4 and R26.

DISCRIMINATOR (A348)

The limiter output is applied to a Foster-Seely type discriminator, where diodes CR1 and CR2 rectify the 455-kHz signal to recover the audio. The discriminator is metered at J442-10 through metering network C16 and R23.

AUDIO - NOISE AMPLIFIER (A348)

The discriminator output is coupled through a low-pass filter (C16, C18, R21 and R22) to the base of audio-noise amplifier Q5. The filter removes any 455-kHz signal remaining in the discriminator output. Q5 operates as an emitter-follower to match the discriminator impedance to the VOLUME control, SQUELCH control, and Channel Guard input. The stage also provides power gain.

AUDIO AMPLIFIERS (A348)

Any audio present in the incoming signal is coupled from the emitter of Q5 through the VOLUME control and a de-emphasis network to the base of audio amplifier Q6. The de-emphasis network consists of C22, C23, R30 and R31.

Audio driver Q7 follows the audio amplifier. The audio output of Q7 is coupled through transformer T1 to provide phase inversion for the push-pull audio PA stage.

Q341 and Q342 operate as a push-pull, class AB audio PA stage. The PA output is coupled through audio transformer T341 to the loudspeaker. The yellow and white tertiary windings of T341 supply balanced feedback to the collector of Q7. The feedback winding minimizes distortion and prevents the pick-up of external electrical noise.

The PA stage provides a 5-watt output at less than 5% distortion into a 3.5-ohm load at the receiver output terminals (3.2-ohms at the Control Unit). Base bias for the PA stage and the elimination of crossover distortion is controlled by bias adjust potentiometer R43. The potentiometer is set at the factory as shown in STEP 1 of the receiver Test Procedure.

- NOTE -

Do not adjust bias adjust potentiometer R43 unless PA transistors Q341 and Q342 have been replaced.

Audio high and low are also present at centralized metering jack J442, and can be used as shown in STEP 1 of the Test Procedure.

SQUELCH (A348)

Noise from the audio-noise amplifier operates the squelch circuit. With no carrier present in the receiver, this noise is coupled to the base of noise amplifier Q8 through a high-pass filter which attenuates frequencies below 3 kHz. The filter consists of C30, C31 and R45, as well as C34 and L3 in the collector circuit of Q8. The gain of Q8 is determined by the Squelch control, which varies the bias on the base of Q8. Thermistor RT2 keeps the critical squelch constant over wide variations in temperature.

The output of noise amplifier Q8 is rectified by diodes CR5 and CR6, and filtered by C36 and C37 to produce a negative DC voltage. This DC voltage is applied to the base of DC amplifier Q9, turning it off. When turned off, the collector voltage of Q9 rises to approximately 8 volts, turning on DC amplifier Q10. When conducting, the collector voltage of Q10 drops to almost ground potential, which removes the base bias to audio amplifier Q6 and audio driver Q7, turning them off.

When the receiver is quieted by a sig-

nal (unsquelched), the noise in the receiver is reduced, turning DC amplifier Q9 on and DC amplifier Q10 off. This allows the audio stages to conduct so that sound is heard in the speaker. A network composed of C38, CR7 and R62 slows down the switching action of Q10, preventing an obnoxious "thump" from being heard in the speaker.

Resistor R53 connects from the emitter of audio driver Q7 to the emitter of noise amplifier Q8, providing a hysteresis loop in the squelch circuit. When a weak signal opens the squelch, the signal level may be reduced by 4 to 6 dB without the squelch closing. This limits squelch "flutter" or "picket-fence" operation.

With audio driver Q7 conducting, a positive voltage through R53 helps to reduce the gain of noise amplifier Q8. This positive feedback provides a quick, positive switching action in the squelch circuit. When the receiver squelches, audio driver Q7 turns off and its emitter potential drops to zero. This reduces the DC feedback through R53 to the emitter of noise amplifier Q8. Reducing the feedback causes Q8 to conduct harder, turning the audio stages off quickly.

Keying the transmitter removes the +10 volts from J19, turning off DC amplifier Q9 and turning on Q10 to mute the receiver.

NOISE BLANKER (A370/A372 - Figure 2)

An RF signal and noise pulse from the antenna is fed simultaneously to the Noise Blanker 1st RF Amplifier and the receiver 1st RF amplifier sections. The signal and noise is transformer coupled through T1/T2/T3 to the base of the first of two RF amplifier stages. The amplifier stages (Q1, Q2) raise the level of the noise pulse which is coupled through T10/T11/T12 and L10 to the base of the pulse detector Q3. A metering network consisting of R22, C21, C17 and R2 permits the blanker to be metered at centralized metering jack J442-11.

Base bias for the pulse detector is established by R9 and CR1. CR1 is normally conducting, which keeps Q3 in a barely conducting state. A noise pulse applied to the base of Q3 causes it to conduct heavily. This results in a negative pulse at the output (collector) of Q3. Following Q3 is a low-pass RF filter consisting of C18, C22 and L5.

The output of the filter is fed to the base of pulse amplifier Q4. This stage is biased by CR3, R12 and R13 so that it is just conducting. The negative-going pulse from the pulse detector cuts CR3 off, which biases Q4 on, and a positive pulse appears at the output of pulse amplifier Q4.

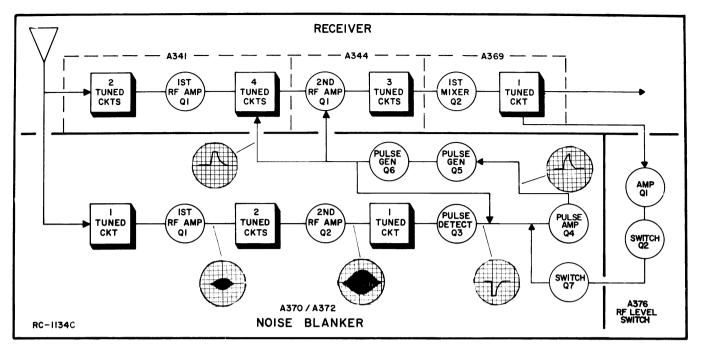


Figure 2 - Noise Blanker Block Diagram

Q5 and Q6 form part of the one-shot multivibrator circuit. Bias voltage through R17 keeps Q5 normally turned on. The positive voltage at the collector of Q5 keeps Q6 turned off. The positive-going pulse from the pulse amplifier (Q4) is fed to the base of Q5, cutting the stage off. As Q5 cuts off, Q6 is turned on; and the output is an 8-volt, 12 to 18 microsecond positive-going blanking pulse. The positive blanking pulse is fed to the emitter of 2nd RF Amplifier A344-Q1 and coil L2. The pulse cuts off Q1 and shunts L2 for the duration of the noise pulse.

The positive blanking pulse to the emitter of the 2nd RF amplifier A344-Q1 is controlled by the RF Level Shut-Off Switch A376. The output of the 1st Mixer is fed through a low-pass filter network in the RF level switch circuit to the base of the high IF level amplifier Q1. When the antenna signal input level is approximately 500-5000 microvolts, the high IF level output of Q1 is sufficient to turn ON level-sensitive switch Q2. The output of Q2 is filtered through C7, C8, L2 and then turns ON the Noise Blanker (A370/A372) switch Q7. The conduction of Q7 changes the bias to the 1st Pulse Amplifier Q4 and shorts the blanking pulse to ground.

The high IF output level (amplified by Q1) is not sufficient to turn Q2 ON when the antenna signal input is below the 500 to 5000 microvolt range. As a result, Q7 does not turn ON, and the positive blanking pulse is fed to the emitter of the 2nd RF Amplifier A344-Q1.

The blanking pulse width is determined

by R17 and C27. Diode CR6 keeps the output pulse a square wave. CR5 prevents oscillation at temperature extremes.

At the same time that the blanking pulse is applied to the receiver, samples of the pulse are fed to automatic repetition rate switch C30, C24, CR4, R13, R14 and R20. The pulse sample is coupled through C30 and is rectified by CR4. The rectified voltage charges C24 which then discharges through R13 and R14 to reverse bias CR3 and turn off pulse amplifier Q4. The components (C23, C24, R13, and R14) are selected so that the output pulses cannot blank the receiver continuously and prevent the desired signal from being heard.

The circuit time constant disables the blanking function whenever sinusoidal intermodulation signals produce beat frequencies of two kHz or higher. However, continuous impulse noise will not disable the blanker until a repetition rate of approximately 10 to 20 kHz is exceeded. The higher impulse noise repetition rate is provided by C23 which bypasses CR3 with the negative-going impulse noise. This turns on Q4 and allows the blanker to function.

As the noise signal from the antenna is applied to the Noise Blanker, the RF signal is applied to the receiver RF amplifier (A341). The six tuned circuits in the receiver front end provide a time delay for the RF signal, which enables the blanking pulse from the noise blanker to cut off the RF amplifier in the receiver before the noise pulse can get there.

The blanker may be disabled by shorting

across the yellow dot on the noise blanker printed wiring board. Refer to the Noise Blanker Troubleshooting Procedure, as listed in the Table of Contents, for a complete performance check.

CHANNEL GUARD

Channel Guard Board Model 4EK16Al0 is a fully transistorized encoder-decoder for use with MASTR Professional Series mobile and station combinations. The tone frequencies are controlled by plug-in tone networks that are made with precision components for excellent stability and reliability. The tone frequencies range from 71.9 to 203.5 Hz.

Encoder (A350)

Keying the transmitter removes the receiver mute +10 volts, and forward biases feedback control diode CR5, causing it to conduct. When conducting, the diode shunts R39, R35 and Cl9). This provides the necessary gain to the base of Q5 to permit oscillation.

The encoder tone is provided by selective amp-oscillator transistors Q5 and Q6 which oscillate at a frequency determined by the tone network. Negative feedback applied through the tone network to the base of Q5 prevents any gain in the stage except at the desired encode frequency.

Starting network R45, C21, C22 and CR6 provide an extremely fast starting time for the encoder tone. Keying the transmitter removes the receiver mute +10 volts, causing a pulse to be applied to the base of Q6 to quickly start the oscillator. Thermistor-resistor combination R32 and RT1 provides temperature compensation for the oscillator output. Limiter diodes CR3 and CR4 keep the tone amplitude constant.

Emitter-follower Q7 follows the oscillator circuit. The encoder tone is taken from the emitter of Q7 and applied to the transmitter.

Decoder (A350)

The decoder function is designed to eliminate all calls that are not tone coded for the Channel Guard frequency. As long as the CHANNEL GUARD-OFF switch on the control unit is left in the CHANNEL GUARD position, all signals are locked out except those from transmitters that are continuously tone coded for positive identification by the receiver.

Placing the CHANNEL GUARD-OFF switch in the OFF position instantly disables the Channel Guard operation so that all calls on the channel can be heard. When the hookswitch option is used, lifting the microphone from its hanger disables the Channel Guard Circuit.

Audio, tone and noise are taken from the emitter of the receiver audio-noise amplifier A348-Q5 and is fed through A350-J1 to four tone amplifier and bandpass filter circuits. The filters remove the audio and high-frequency noise from the signal, and the tone amplifiers provide sufficient gain to insure clipping by limiter diodes CR1 and CR2. The clipping action eliminates variation in the squelch performance due to changes in tone deviation. The signal is then applied to selective amplifiers Q5 and Q6 which amplify only the tone determined by the tone network.

The output of the selective amplifier is applied through emitter-follower Q7 to the high gain, broad-band tone amplifiers Q8 and Q9. The output of Q9 is rectified by detector diodes CR7 and CR8, and the resulting negative DC voltage controls the squelch gate. Q8 is normally biased for low gain. When the tone is detected by CR7 and CR8, feedback is provided through R54 to quickly change the bias on Q8 for full gain. This ensures a more positive "unsquelching" action.

Squelch gate diode CR9 is normally forward biased by a positive DC voltage (approximately 1.5 volts) fed through R58. The forward bias causes CR9 to conduct, feeding a DC voltage to the base of DC amplifier A348-Q10 in the receiver. This removes the bias on the receiver audio stages and holds them off.

When the proper tone is applied to the decoder, the negative DC voltage from the detector diodes back-biases squelch gate diode CR9 and cuts off the positive bias to the receiver DC amplifier A348-Q10. However, the receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

Placing the CHANNEL GUARD - OFF switch in the OFF position (or removing the microphone from its hookswitch) removes the ground to the base of the decoder DC switch (Q10), causing it to conduct. This backbiases squelch control diode CR9 and cuts off the positive bias to the receiver DC amplifier (A348-Q10). The receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

A tone rejection filter connected in parallel with A348-J12 (in the receiver) bypasses any incoming tone to ground. This attenuates the tone level reaching the receiver audio circuits. The filter is composed of C26, C27, C28, C29, L1 and R59.

An optional tone reject filter (A402) that is identical to the filter described above is available for use in two-way radios with transmitter Channel Guard only.

MAINTENANCE

DISASSEMBLY

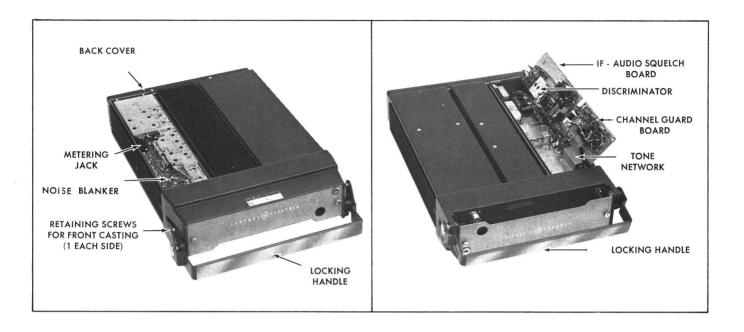


Figure 3 - Removing Top Cover

To service the receiver from the top--

- 1. Pull locking handle down and pull radio about one inch out of mounting frame.
- 2. Pry up cover at rear of receiver.
- 3. Slide cover back and lift off.

- Loosen the two Phillips-head retaining screws in front casting (see Figure 3), and pull casting away from system frame.
- 2. Remove the four screws in the back cover.
- Remove the two screws holding the receiver at each end of the system frame.
- 4. Disconnect the antenna jack and the 20-pin connector from the front of the receiver, and slide the unit out of the system frame.

Figure 4 - Removing Bottom Cover

To service the receiver from the bottom--

- Pull locking handle down. Pull radio out of mounting frame.
- Remove screws in bottom cover. Pry up cover at back of receiver.
- 3. Slide cover back and lift off.

FRONT END ALIGNMENT

EQUIPMENT REQUIRED

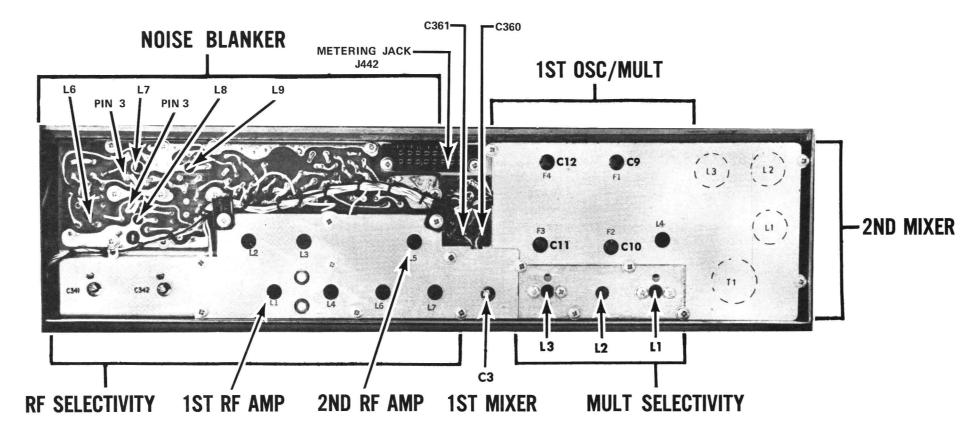
- 1. GE Test Set Models 4EX3A10, 4EX8K10, 11 (or 20,000 ohms-per-volt Multimeter with a
- A 455 kHz and 25-50 MHz signal source. Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.

PRELIMINARY CHECKS AND ADJUSTMENTS

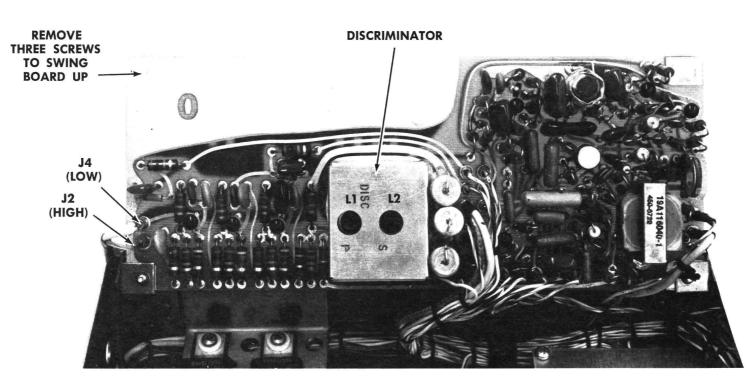
- Connect Test Set to Receiver Centralized Metering Jack J442 and set meter sensitivity switch to the TEST 1 position (or 1-volt position on 4EX8K10, 11).
- With Test Set in Position J, check for regulated +10 volts. If using Multimeter, measure from C360 to C361.
- 3. If using Multimeter, connect the positive lead to J442-16 (Ground).
- 4. Disable Channel Guard.

ALIGNMENT PROCEDURE

	METERI	NG POSITION			
STEP	GE Test Set	Multimeter - at J442	TUNING CONTROL	METER READING	PROCEDURE
			OSCILLATOR/MULTI	PLIER	
1.	D (MULT-1)	Pin 4	L4 (on 1st OSC/MULT) and L1, L2 (on MULT SELECTIVITY)	See Pro- cedure	Tune L4 on 1st OSC/MULT and L1 on MULT SELECTIVITY for maximum meter reading. Next, tune L2 for minimum meter reading. Then tune L3 for maximum meter reading. Repeat step 1, changing voltage scale if necessary.
			RF AMPLIFIER & SELE	CTIVITY	
2.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal adjacent to L7. Adjust the signal generator for discriminator zero.
3.	B (2nd IF Amp)	Pin 2	L1 (1st RF Amp), L6, L7, C341 and C342 (RF SELEC- TIVITY)	Maximum	Apply an on-frequency signal to the antenna jack, keeping below saturation. Tune L1 thru L7, C341, and C342 for maximum meter reading.
4.	"	"	L4 (1st OSC/MULT) and L1 and L2 (MULT SELECTIVITY)	Maximum	Apply an on-frequency signal as above, keeping below saturation. Tune L4 on 1st OSC/MULT and L1, L2 and L3 on MULT SELECTIVITY for maximum meter reading.
			FREQUENCY ADJUST	MENT	
5.	A (DISC)	Pin 10	C9 on 1st OSC (C10, C11 or C12 for multi- frequency)	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required.
					For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50° to 90°F.



IF-AUDIO & SQUELCH



COMPLETE RECEIVER & NOISE BLANKER ALIGNMENT

EQUIPMENT REQUIRED

- 1. GE Test Set Models 4EX3A10, 4EX8K10, 11 (or 20,000 ohms-per-volt Multimeter with a 1-volt scale).
- 2. A 455 kHz signal cource (GE Test Set Model 4EX7A10) and 25-50 MHz signal cource. Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.

PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Connect Test Set to Receiver Centralized Metering Jack J442, and set meter sensitivity switch to the TEST 1 position (or 1-volt position
- 2. For large changes in frequency or a badly mis-aligned receiver, set crystal trimmer C9 to mid-capacity. In multi-frequency receivers, set C10, C11 or C12 to mid-capacity as required. Where the maximum frequency spacing is less than 100 kHz, align the unit on channel F1. If the frequency spacing is greater than 100 kHz, align the receiver on the center frequency.
- 3. With Test Set in Position J, check for regulated +10 volts. If using Multimeter, measure from C360 to C361.
- 4. If using Multimeter, connect the positive lead to J442-16 (Ground).
- 5. For large changes in frequency or a badly mis-aligned receiver, adjust all slugs on the Noise Blanker to the bottom of the coil form (closest to printed wiring board).
- Disable the Channel Guard.

ALIGNMENT PROCEDURE

	METERIN	NG POSITION			
TEP	GE Test Set	Multimeter - at J442	TUNING CONTROL	METER READING	PROCEDURE
				DISCRIMINAT	FOR & OSCILLATOR
1.	A (DISC)	Pin 10	L1 and L2 (on IF-AUDIO SQUELCH board)	Zero	Remove three screws and swing open the IF-AUDIO & SQUELCH board. Adjust L1 (disc primary) 1/2 turn counterclockwise from the bottom of coil. Next, apply a 455-kHz signal to J2 and J4 and adjust L2 (disc secondary) for zero meter reading.
2.	A (DISC)	Pin 10		See Pro- cedure	Alternately apply a 450-kHz and 460-kHz signal and check for readings of at least 0.3 volt, but not more than 0.5 volt on GE Test Set. Both readings must be within .05 volt. Do not attempt to balance readings any closer than 0.05 v.
3.	D (MULT-1)	Pin 4	L4 (on 1st OSC/MULT) and L1, L2 & L3 (on MULT SELECTIVITY)	See Pro- cedure	Tune L4 on 1st OSC/MULT and L1 on MULT SELECTIVITY for maximum meter reading. Tune L2 for minimum meter reading. Change voltage scale if necessary. Then tune L3 for maximum meter reading. Repeat step 3.
			RJ	F AMPLIFIERS	S & SELECTIVITY
4.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal adjacent to L6 (RF SELECTIVITY). Adjust the signal generator for discriminator zero.
5.	B 2nd IF AMP	Pin 2	L7, L6, L4, L3 and L2 (RF SELECTIVITY) L5 (2nd RF AMP)	Maximum	Apply an on-frequency signal and tune as shown below, keeping signal below saturation. Apply Signal Generator Probe To: L6 L4 L4 L1 (1st RF AMP) L4, L3 and L2
6.	B 2nd IF AMP	Pin 2	C341, C342 (RF SELECTIVITY) and L1 (1st RF AMP)	Maximum	Apply an on-frequency signal to antenna jack J441. Tune C341, C342 at L1 for maximum meter reading, keeping signal below saturation.
7.	"	"	L7, L6, L4, L3, L2, C342 and C341 (RF SELECTIVITY), L5 (2nd RF AMP), L1 (1st RF AMP)	Maximum	Apply an on-frequency signal as above, keeping below saturation. Tune L7, L6, L5, L4, L3, L2, L1, C342 and C341 for maximum meter reading.
8.	"	"	L3 on MULT SELECTIVITY	Maximum	Apply an on-frequency signal as above, keeping below saturation. Tune L2 and L3 on MULT SELECTIVITY Board for maximum meter reading.

The 1st and 2nd mixer, and low IF circuits have been aligned at the factory and will normally require no further adjustment. If adjustment is necessary, use the procedure outlined in STEPS 9, 10, and 11. C3 does not peak, but provides impedance matching for the crystal filter input and should only be tuned when observing IF trace on oscilloscope.

Refer to DATAFILE BULLETIN 1000-6 IF Alignment of Two-Way Radio FM Receivers for helpful suggestions on how to determine when IF Alignment is required.

9.	B (2nd IF AMP)	Pin 2	L3, L2, L1, T1 (2nd Mixer)	Maximum	Apply on-frequency, unmodulated signal and tune L3, L2, L1, and T1 for maximum meter reading, keeping signal below saturation.
10.			A347-L3, L2, L1, T1 (2nd Mixer)		Connect scope, signal generator, and detector as shown in Figure 5. Set signal generator level for 30-50 μV and modulate with 10 kHz at 20 Hz. With detector at the collector of Q3 (2nd mixer board output), tune for double trace as shown on scope pattern.
11.	(DISC)	Pin 10	-	See Pro- cedure	Check to see that discriminator idling voltage is within $\pm .05$ volt of zero with no signal applied. Check to see that modulation acceptance bandwidth is between ± 7 and 9 kHz.

ALIGNMENT PROCEDURE

METERING POSITION

			•		
EP	GE Test Set	Multimeter - at J442	TUNING CONTROL	METER READING	PROCEDURE
				NOISE	BLANKER
2.	H (BLANKER)	Pin 11 (-) and Pin 16 (+)	L9, L8, L7 and L6 on NOISE BLANKER	Maximum	Apply a signal according to the following table: Receiver operating frequency 25-27 MHz 27-33 MHz 4 MHz above operating freq. 4 MHz below operating freq. 4 MHz below operating freq. 4 MHz below operating freq. 4 MHz above operating freq. 4 MHz above operating freq. 4 MHz above operating freq. 5 MHz 4 MHz above operating freq. 5 MHz 5 MHz 6 MHz 6 MHz 7 MHz 7 MHz 7 MHz 8 MHz 9 (2nd peak) 1 MHz 1 MHz 1 MHz 8 MHz 8 MHz 9 MHz 1 MHz 8 MHz 8 MHz 9 MHz 1 MHz 9 MHz 1 MHz 9 MHz 1
.3.	"	"	11	Maximum	Apply signal on blanker frequency to the antenna jack. Retune L6, L8 and L9 for maximum meter reading.
4.	"	"	11	0.1 y	Apply a 1,000-microvolt signal on blanker frequency to antenna jack Reading should be approximately 0.1 volt.
				FREQUENCY	ADJUSTMENT
5.	A (DISC)	Pin 10	C9 on 1st OSC (C10, C11 or C12 for multi-frequency	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or as required. NOTE For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is a a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperaturange of 50° to 90°F.

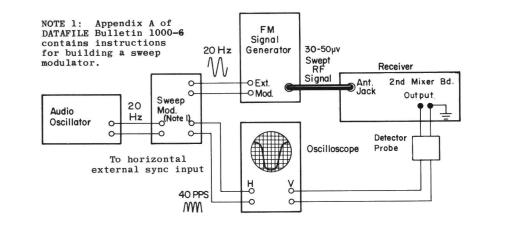


Figure 5 - Test Setup for 20-Hz Double-Trace Sweep Alignment

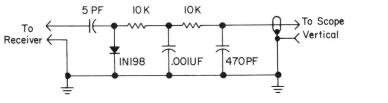


Figure 6 - Detector Probe for Sweep Alignment

ALIGNMENT PROCEDURE

25—50 MHz MASTR RECEIVER

MODELS 4ER39C28-45

Issue 4

LBI-3925

LBI-3925

SIGNAL GENERATOR

DEVIATION

ANTENNA

(CONNECTS TO J443)

TEST PROCEDURES

These Test Procedures are designed to help you to service a receiver that is operating——but not properly.

The problems encountered could be low power, poor sensitivity, distortion, limiter not operating properly, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized.

Once the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

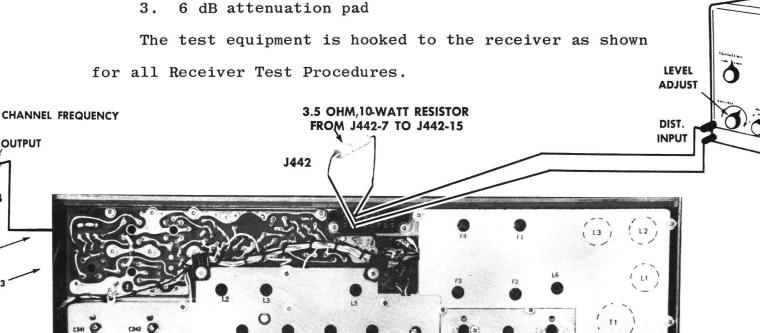
DISTORTION ANALYZER

PIN 2 REMOVED FROM

TEST EQUIPMENT REQUIRED

for test hookup shown:

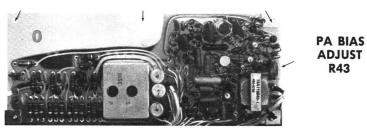
Distortion Analyzer similar to: Heath #1M-12
 Signal Generator similar to: Measurements #M-560



COMPONENT TOP VIEW



REMOVE THREE SCREWS AND SWING BOARD OPEN



IF-AUDIO & SQUELCH BOARD (COMPONENT VIEW)

STEP 1

AUDIO POWER OUTPUT AND DISTORTION TEST PROCEDURE

Measure Audio Power Output as follows:

- A. Connect a 1,000-microvolt test signal modulated by 1,000 hertz ±3.3 kHz deviation to the antenna jack J441.
- B. With Five-Watt Speaker:

Disconnect speaker lead pin from J701-2 (on rear of Control Unit).

Connect a 3.5-ohm load resistor from J442-15 to J442-7. Connect the Distortion Analyzer input across the resistor as shown.

OR



5-WATT

VOLTMETER SCALE ON DISTORTION ANALYZER

With Handset:

Lift the handset off of the hookswitch. Connect the Distortion Analyzer input from J442-15 to J442-7.

- C. Set the VOLUME control for five-watt output (4.18 VRMS).
- D. Make distortion measurements according to manufacturer's instructions. Reading should be less than 5%.

SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than five watts, make the following checks:

- E. Battery and regulator voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)
- F. P.A. Bias Adjust (R43) -- Turn the SQUELCH control fully counterclockwise. Then connect a milliammeter in series with the +12-volt lead at P443-11. With no signal in, adjust R43 for a reading of approximately 20 milliamps. This adjustment should not be necessary unless an output transistor has been replaced.
- G. Audio Gain (Refer to Receiver Troubleshooting Procedure).
- H. Discriminator Alignment (Refer to Receiver Alignment on reverse side of page).

STEP 2

USABLE SENSITIVITY (12 db SINAD)

TEST PROCEDURE

Measure sensitivity of the receiver modulated at the standard test modulation as follows:

- A. Be sure Test Step 1 checks out properly.
- B. Reduce the Signal Generator output from setting in Test Step 1A.
- C. Adjust Distortion Analyzer LEVEL control for a +2 dB reading.
- D. Set CONTROL from LEVEL to DISTORTION reading. Repeat Steps 2B and 2C until difference in reading is 12 dB (+2 dB to -10 dB).
- E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is "usable" sensitivity level. Reading should be less than 0.25 microvolts with audio output at least 2.5 watts (2.9 volts RMS across the 3.5-ohm receiver load).

SERVICE CHECK

If the sensitivity level is more than 0.25 microvolts, make the following checks:

- F. Alignment of RF stages (Refer to RF Alignment in Receiver Alignment on reverse side of page).
- G. Gain measurements as shown on the Receiver Troubleshooting Procedure.

STEP 3

MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH) TEST PROCEDURE

- A. Be sure Test Steps 1 and 2 check out properly.
- B. Set Signal Generator output for twice the microvolt reading obtained in Test Step 2D.
- C. Increase Signal Generator frequency deviation.
- D. Adjust LEVEL Control for +2 dB.



E. Set CONTROL from LEVEL to DISTORTION reading. Repeat Steps 3C, 3D and 3E until difference between readings becomes 12 dB (from +2 dB to -10 dB).



LEVEL

F. Deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than ± 7 kHz (but less than ± 9 kHz).

SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

TROUBLESHOOTING PROCEDURE

Before starting the Noise Blanker troubleshooting procedure, make sure the receiver is operating properly. Align the Noise Blanker as described on the ALIGNMENT PROCEDURE Sheet. Then make the following Troubleshooting checks:

STEP 1—PERFORMANCE CHECK

Equipment Required:

- RF Signal Generator coupled through a 6 db pad.
- Pulse Generator with repetition rate and level controls (similar to General Electric Model 4EX4A10)
- AC VTVM

Procedure:

1. Connect Pulse Generator and RF Signal Generator to receiver antenna jack through a T-connector and connect VTVM to receiver output as shown in Figure 1.

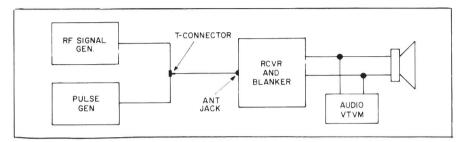


Figure 1 - Equipment Connection Diagram

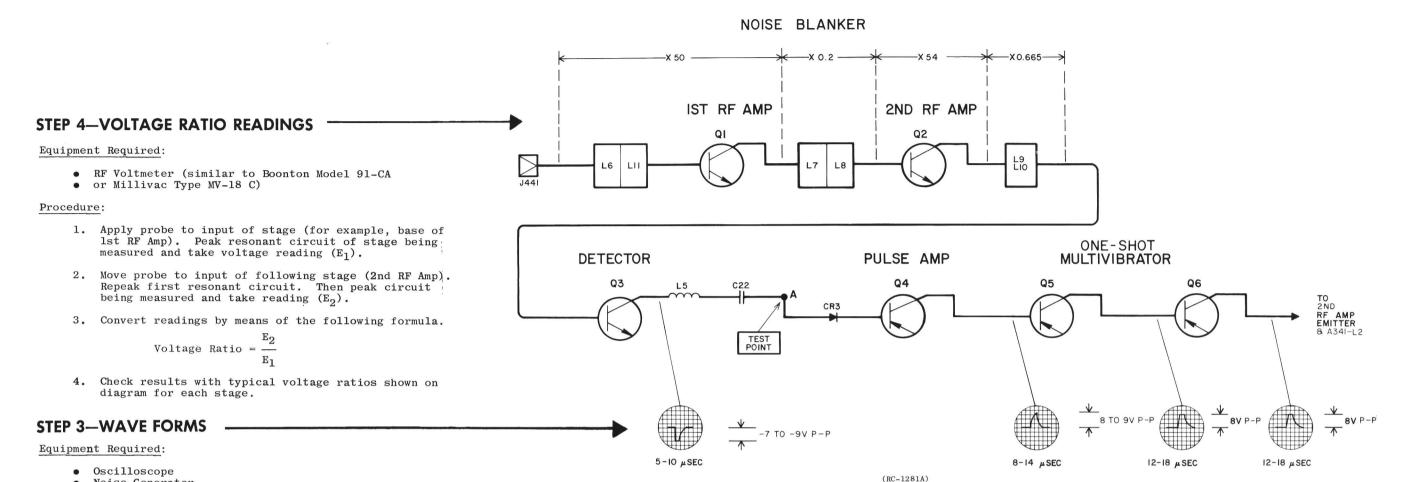
- 2. Apply an unmodulated RF Signal and check the 20 db quieting sensitivity of the receiver. (Measure with Model 4EX4A10 Pulse Generator connected but turned off).
- 3. Disable pulse section of the noise blanker by shorting Q4 base to emitter. (A yellow dot is located between the base and emitter connections on solder side of the noise blanker board).
- 4. Set the pulse generator (Model 4EX4A10) repetition rate to 1500 Hz and adjust the output level control on pulse generator until receiver sensitivity is degraded as much as possible (approximately 45 db).
- 5. Remove base-emitter short from Q4. The receiver sensitivity should restore to within 5 db of 20 db quieting level obtained in step 2 above.

STEP 2—QUICK CHECKS

Equipment Required:

Audio Voltmeter (VTVM)Audio Oscillator (sine wave)

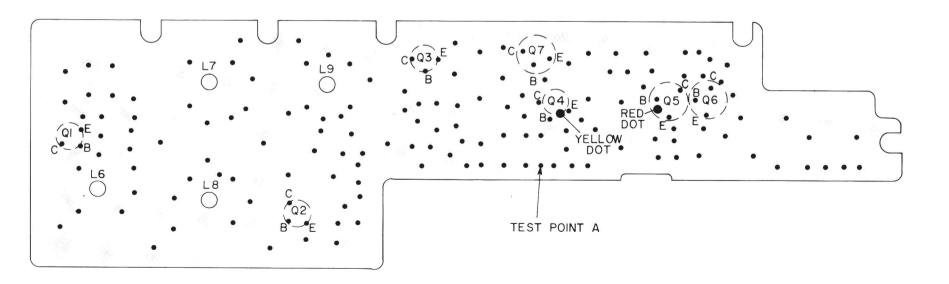
SYMPTOMS	PROCEDURE
No regulated 10-volts	Check the 12-volt supply. Then check regulator circuit. (Refer to troubleshooting procedure for power supply.
No blanking	Check waveforms (STEP 3) and voltage ratios (STEP 4).
Partial or no blanking	a. Check RF attenuation as follows: Connect signal generator to Antenna Jack. Adjust the output of the signal generator for 0.2 volts on the 2nd IF amplifier (position B on test set) and note the signal generator reading. Short the Q5 base to emitter pattern (identified by red ink dot) and increase the signal generator output until the same 2nd IF amplifier reading is obtained. Signal level must in- crease 60 db or more.
	b. Check repetition rate switch. Connect a 6-kHz sine wave signal from audio oscillator through a 0.33-μf capacitor to point "A" located on the noise blanker board. Adjust the output of the audio oscillator for 2-volts, peak-to-peak. Observe the output of the pulse generator (on noise blanker) with an oscilloscope. The repetition rate of the pulse generator should not increase over 2 kHz or decrease under 1 kHz. (This is true for sine wave inputs like intermodulation in the blanker channel but not for strong impulse noise from antenna.)
	c. Check vehicle ignition system. Worn-out points, bad spark plugs, or breaks in ignition wiring can cause a "dirty" igni- tion pulse to be generated causing the blanker to operate in- correctly.



Procedure:

• Noise Generator

Adjust noise generator for maximum output level and observe waveforms on oscilloscope at the indicated points.



TROUBLESHOOTING PROCEDURE

LBI-3925

NOISE BLANKER FOR 25—50 MHZ RECEIVER TYPE ER-39-C

Issue 2

Denotes Solder Side

(RC-1693) (19B204655, Sh. 2, Rev. 3)

STEP 1 - QUICK CHECKS

TEST SET CHECKS

These checks are typical voltage readings measured with GE Test Set Model 4EX3AlO in the Test 1 position, or Model 4EX8KlO or 11 in the 1-volt position.

Metering Position	Reading With No Signal In	Reading with 1 Micro- volt Unmodulated
A (Disc Idling)	Less then ±.05 VDC	
B (2nd IF)	.15 VDC	.7 VDC
C (1st Lim)	.7 VDC	0.8 VDC
D (Mult-1)	0.6 VDC	
J (Reg. +10 volts)	+10 VDC	

SYMPTOM CHECKS

SYMPTOM	PROCEDURE
NO SUPPLY VOLTAGE	• Check power connections and continuity of supply leads, and check fuse in power supply. If fuse is blown, check receiver for short circuits.
NO REGULATED 10-VOLTS	• Check the 12-volt supply. Then check regulator circuit. (See Troubleshooting Procedure for Power Supply).
LOW 1ST LIM READING	• Check supply voltages and then check oscillator reading at J442-4 & 5 as shown in STEP 2A.
	Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 1st Limiter stages as shown in STEP 2A.
LOW OSCILLATOR/MULTI- PLIER READINGS	• Check alignment of Oscillator. (Refer to Front End Alignment Procedure).
	• Check voltage and resistance readings of 1st Oscillator/Multiplier Q1/Q2.
	• Check crystal Y1.
LOW RECEIVER SENSITIVITY	• Check Front End Alignment. (Refer to Receiver Alignment Procedure).
	Check antenna connections, cable and relay.
	• Check 1st and 2nd Oscillator injection voltage.
	• Check voltage and resistance readings of 1st Mixer, HI IF Amp and 2nd Mixer.
	• Make SIMPLIFIED GAIN CHECKS (STEP 2A).
LOW AUDIO	Check Audio PA (Q341 & Q342) voltage readings on schematic diagram.
	• Make simplified gain and waveform checks of audio and squelch stages. (Steps 2A and 2B).
	Make unsquelched voltage readings in Audio section. (Refer to Receiver Schematic Diagram).
	• Check voltage and resistance readings on Channel Guard board.
HIGH DISTORTION AT LOW AUDIO LEVELS (50 MW)	Set PA bias adjust R43 as specified under Service.
	• Checks in STEP 1 of TEST PROCEDURES.
IMPROPER SQUELCH OPERATION	• Check voltage and resistance readings of Squelch circuit. (Refer to Receiver Schematic Diagram).
	• Make gain and waveform checks of audio and squelch stages. (Steps 2A and 2B).
DISCRIMINATOR IDLING TOO FAR OFF ZERO	See if discriminator zero is in center of IF bandpass.

STEP 3-VOLTAGE RATIO READINGS ---

QUIPMENT REQUIRED:

- RF VOLTMETER (SIMILAR TO BOONTON MODEL 91-CA OR MILLIVAC TYPE MV-18 C.
- SIGNAL ON RECEIVER FREQUENCY (BELOW SATURATION).
 CORRECT FREQUENCY CAN BE DETERMINED BY ZEROING
 THE DISCRIMINATOR. USE 1,000 HERTZ SIGNAL WITH
 3,3 KHZ DEVIATION.

PROCEDURE:

- 1. APPLY PROBE TO INPUT OF STAGE (FOR EXAMPLE, BASE OF RF AMP). PEAK RESONANT CIRCUIT OF STAGE BEING MEASURED AND TAKE VOLTAGE READING (E₁).
- 2. MOVE PROBE TO INPUT OF FOLLOWING STAGE.
 REPEAK FIRST RESONANT CIRCUIT THEN PEAK CIRCUIT
 BEING MEASURED AND TAKE READING (E2).
- 3. CONVERT READINGS BY MEANS OF THE FOLLOWING FORMULA.

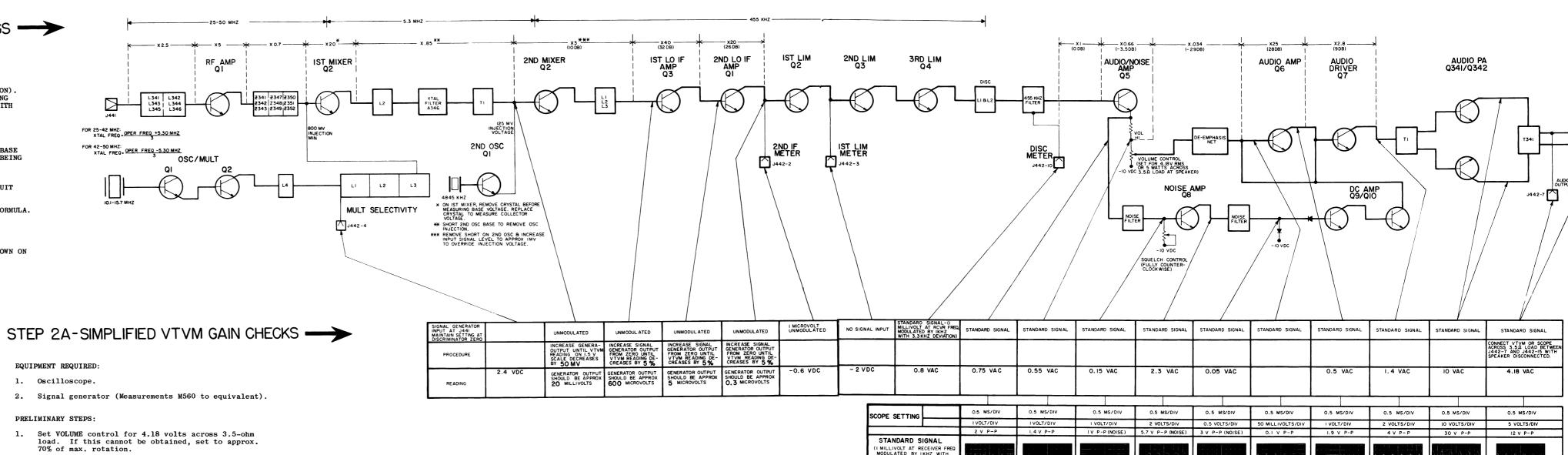
4. CHECK RESULTS WITH TYPICAL VOLTAGE RATIOS SHOWN ON DIAGRAM.

2. Set SQUELCH control fully counterclockwise.

4. Connect oscilloscope between system negative and

3. Receiver should be properly aligned.

points indicated by arrow.



STEP 2B-AUDIO & SQUELCH WAVEFORMS ->

EQUIPMENT REQUIRED:

- 1. VTVM AC & DC
- 2. Signal generator (Measurements M560 to equivalent).

PRELIMINARY STEPS:

- Set VOLUME control for 4.18 volts across 3.5-ohm load. If this cannot be obtained, set to approx. 70% of max. rotation.
- 2. Set SQUELCH control fully counterclockwise.
- 3. Receiver should be properly aligned.
- Connect VTVM between system negative and points indicated by arrow.

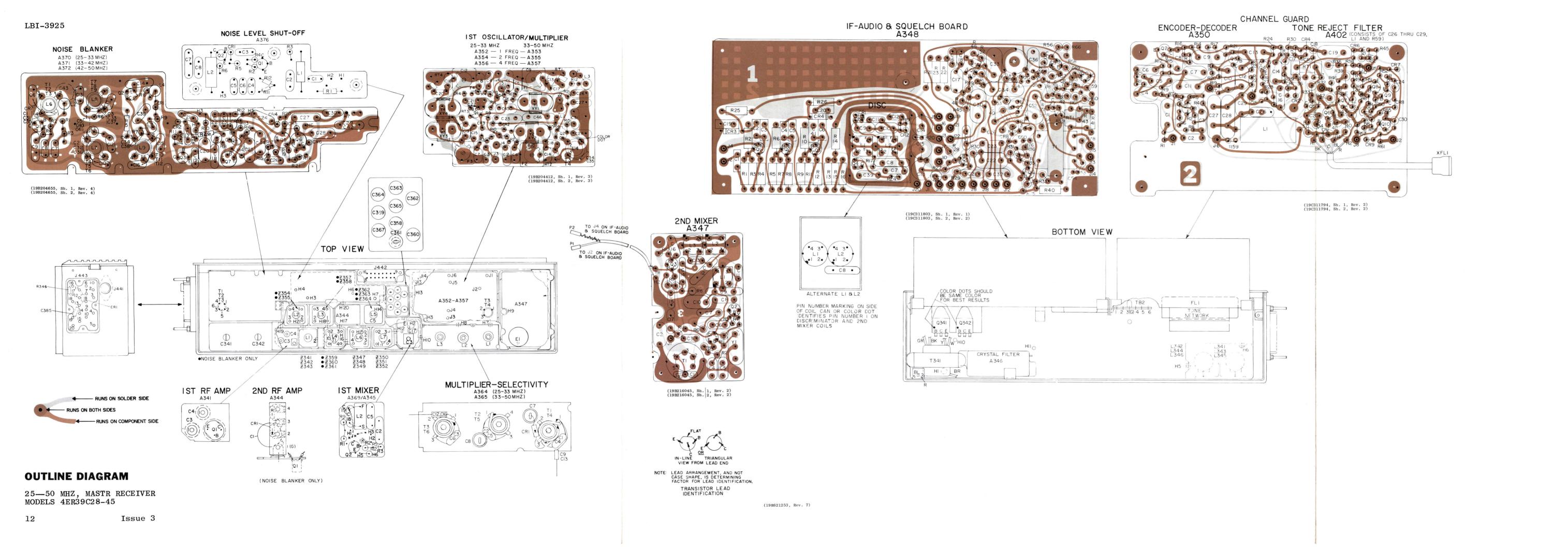
(RC-1687A)

NOISE WAVE FORM

TROUBLESHOOTING PROCEDURE

25—50 MHZ, MASTR RECEIVER MODELS 4ER39C28-45

Issue 2



														_								·	
		PARTS LIST	SYMBO	OL G-E PART NO	DESCRIPTION	SYMBO	G-E PART NO	DESCRIPTION	SYMBO	L G-E PART NO	DESCRIPTION	SYMBO	L G-E PART NO	DESCRIPTION	SYMBO	G-E PART NO	DESCRIPTION	SYMBO	G-E PART NO	DESCRIPTION	SYMBOL	G-E PART NO	DESCRIPTION
		LBI-3915B 25-50 MHz RECEIVER	C2 C3	19B209243-P7 5494481-P112	Polyester: 0.1 \(\mu f \pm 20\%, 50 \) VDCW. Ceramic disc: .001 \(\mu f \pm 10\%, 1000 \) VDCW; sim	A348		IF AUDIO AND SQUELCH 19D413129-G1 REV A	C38*	5496267-P10 5496267-P14	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. Earlier than REV A.	R10 R11	3R77-P153J 3R77-P823K	Composition: 15,000 ohms ±5%, 1/2 w. Composition: 82,000 ohms ±10%, 1/2 w.	R55	3R77-P103K 3R77-P224J	Composition: 10,000 ohms ±10%, 1/2 w. Composition: 0.22 megohms ±5%, 1/2 w.	C18	5496267-P1	Tantalum: 6.8 μ f \pm 20%, 6 VDCW; sim to Sprague Type 150D.	Q5 thru Q8	19Al 15362-Pl	Silicon, NPN; sim to Type 2N2925.
		ODELS 4ER39C28 - 4ER39C45	C4 and	54 90 00 8-P3 5	to RMC Type JF Discap. Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C1	5494481-P111		C39	19B209243-P1	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. Polyester: 0.01 µf ±20%, 50 VDCW.	R12 R13	3R77-P472K 3R77-P272K	Composition: 4700 ohms ±10%, 1/2 w. Composition: 2700 ohms ±10%, 1/2 w.	R57 R58	3R 77-P103K 3R 77-P181K	Composition: 10,000 ohms ±10%, 1/2 w. Composition: 180 ohms ±10%, 1/2 w.	C19 C20	19B209243-P117 5494481-P111	Polyester: 0.047 µf ±10%, 50 VDCW. Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	Q9 and Q10	19Al 15123-P1	Silicon, NPN; sim to Type 2N2712.
SYA	ABOL G-E PART NO	. DESCRIPTION	C6	5490008-P9	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C2	5496219-P717	RMC Type JF Discap. Ceramic disc: 47 pf ±10%, 500 VDCW, temp coef -750 PPM.	C40*	5496267-P28 19B209243-P117	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Earlier than REV A. Polyester: 0.22 µf ±10%, 50 VDCW.	R14 R15	3R 77-P103J 3R 77-P333J	Composition: 10,000 ohms ±5%, 1/2 w. Composition: 33,000 ohms ±5%, 1/2 w.	R59 R60	3R 77-P393K 3R 77-P103K	Composition: 39,000 ohms ±10%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w.	C21		Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	Rl	3R 15 2- P6 82K	RESISTORS
A34	1	RF AMPLIFIER ASSEMBLY	C7 and C8	19B209243-P5	Polyester: 0.047 μf ±20%, 50 VDCW.	СЗ	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C41	5490008-P129	Silver mica: 120 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	R16 R17	3R 77-P181K 3R 152-P471J	Composition: 180 ohms ±10%, 1/2 w. Composition: 470 ohms ±5%, 1/4 w.	R61 R62*	3R 77-P103K	*Composition: 10,000 ohms ±10%, 1/2 w.	C22	5496267-P17 5496267-P13	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Tantalum: 2.2 µf ±20%, 20 VDCW; sim to	R2 R3	3R 15 2-P6 83 J 3R 15 2-P8 22 J	Composition: 68,000 ohms ±5%, 1/4 w. Composition: 8200 ohms ±5%, 1/4 w.
		198204772-G1	C9	5496219-P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.	C4	5496219-P717 5494481-P111	Ceramic disc: 47 pf ±10%, 500 VDCW, temp coef -750 PPM.	C42*	19B209243-P4 5496267-P213	Polyester: 0.033 µf ±20%, 50 VDCW. Deleted by REV A. Tantalum: 2.2 µf ±10%, 20 VDCW; sim to	R18 and R19	3R152-P513J	Composition: 51,000 ohms ±5%, 1/4 w.	R63*	3R77-P223K 3R77-P432J	Earlier than REV A. Composition: 22,000 chms ±10%, 1/2 w. Composition: 4300 chms ±5%, 1/2 w.	C24	5496267-P1	Sprague Type 150D. Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.	R4 R5	3R152-P152J 3R152-P682K	Composition: 1500 ohms ±5%, 1/4 w. Composition: 6800 ohms ±10%, 1/4 w.
,	C1 5494481-P12	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C10 C11	19B209243-P7 5496219-P40	Polyester: 0.1 µf ±20%, 50 VDCW. Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.	and C6	19 B209 243-P5	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C49*	5496267-P9	Sprague Type 150D. Deleted by REV A. Tantalum: 3.3 µf ±15%, VDCW; sim to Sprague	R20 R21	3R152-P472K 3R77-P362J	Composition: 4700 ohms ±10%, 1/4 w. Composition: 3600 ohms ±5%, 1/2 w.	R64	3R 77-P180J	Deleted by REV A. Composition: 18 ohms ±5%, 1/2 w.	C25	5496267-P18	Tantalum: 6.8 μ f \pm 20%, 35 VDCW; sim to Sprague Type 150D.	R6 R7	3R152-P201J 3R152-P113J	Composition: 200 ohms ±5%, 1/4 w. Composition: 11,000 ohms ±5%, 1/4 w.
	C2 5494481-P14 C3 5493392-P7	Ceramic disc: .002 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C12		Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.	C8	5496219-P369	Polyester: 0.047 µf ±20%, 50 VDCW. Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150.	C50*	19B209243-P7	Type 150D. Added by REV. A. Polyester: 0.1 µf ±20%, 50 VDCW. Added by REV. A.	R22 R23	3R77-P104K	Composition: 0.1 megohms ±10%, 1/2 w.	R65*	3R 77-P154K 3R 77-P472K	Composition: 0.15 megohms ±10%, 1/2 w. Deleted by REV A. Composition: 4700 ohms ±10%, 1/2 w.	C26 C27 and	1	Polyester: 0.068 μf ±5%, 50 VDCW. Polyester: 0.33 μf ±10%, 250 VDCW.	R8*	3R152-P622J 3R152-P512J	Composition: 6200 ohms $\pm 5\%$, $1/4$ w. Earlier than REV A. Composition: 5100 ohms $\pm 5\%$, $1/4$ w.
	33 5493392-P7 and 34	Ceramic, feed-thru: .001 µf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.	C13	5496219-P40 5496219-P471	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM. Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef	C9 and C10	5490008-P37	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C51*	5494481-P127	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV. A.	R24 R25	3R 15 2-P1 02J 3R 77-P103K	Composition: 1000 ohms ±5%, 1/4 w. Composition: 10,000 ohms ±10%, 1/2 w.	R75*	3R77-P473J	Composition: 47,000 ohms $\pm 5\%$, $1/2$ w. Added by REV A.	C28 C29	19B209243-P107	Polyester: 0.1 μf ±10%, 50 VDCW.	R9 R10	3R 15 2-P113J 3R 15 2-P512J	Composition: 11,000 ohms ±5%, 1/4 w. Composition: 5100 ohms ±5%, 1/4 w.
	Q1 19A115342-P1	TRANSISTORS	C15	7491395-P109	-220 PPM. Ceramic disc: .001 µf ±10%, 500 VDCW; sim to RMC Type JL.	C11	5496219-P656	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -470 PPM.	C52*		Polyester: 0.22 µf ±10%, 50 VDCW. Added by REV. A.	and R26 R27	38.77-P753J	Composition: 75,000 ohms ±5%, 1/2 w.	R76*		Composition: 9100 ohms ±5%, 1/4 w. Added by REV A. Composition: 5600 ohms ±5%, 1/4 w.	C30	5496267-P17	Tantalum: 1.0 μf $\pm 20\%$, 35 VDCW; sim to Sprague Type 150D.	R11 R12	3R 15 2-P103J 3R 152-P822J	Composition: 10,000 ohms $\pm 5\%$, $1/4$ w. Composition: 8200 ohms $\pm 5\%$, $1/4$ w.
		RESISTORS	C16	19B209243-P5 19B209243-P1	Polyester: 0.047 \(\mu f \pm \)20%, 50 VDCW. Polyester: 0.01 \(\mu f \pm \)20%, 50 VDCW.	C12 C13	5494481-P108 19A115680-P107	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. Electrolytic: 100 µf +150% -10%, 15 VDCW; sim	C53* and C54*	5496267-P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague Type 150D. Added by REV. A.	and R28 R29	3R 77-P182J	Composition: 1800 ohms ±5%, 1/2 w.	R78*	3R 77-P100J	added by REV A. Composition: 10 ohms ±5%, 1/2 w. Added by REV A.	CR1	19A115250-P1	DIODES AND RECTIFIERS	R13 R14	3R152-P153J 3R152-P133J	Composition: 15,000 ohms ±5%, 1/4 w. Composition: 13,000 ohms ±5%, 1/4 w.
•	3R 15 2-P302J	Composition: 12,000 ohms ±10%, 1/4 w. Composition: 3000 ohms ±5%, 1/4 w.	52.7	100200245-F1	Added by Rev A.	C14 and	19Al15680-Pl04	to Mallory Type TT.	CR1 and	19A115250-P1	DIODES AND RECTIFIERS	R30	3R 77-P102J 3R 77-P821J	Composition: 820 ohms ±5%, 1/2 w. Composition: 820 ohms ±5%, 1/2 w.	R79*	3R 15 2-P393J	Composition: 39,000 ohms ±5%, 1/4 w. Added by REV A.	CR2	5494922-P1	Silicon.	R15 R16	3R152-P510J 3R152-P153J	Composition: 51 ohms ±5%, 1/4 w. Composition: 15,000 ohms ±5%, 1/4 w.
i	3R 15 2-P1 02 K 3R 15 2-P3 91 K	Composition: 1000 ohms ±10%, 1/4 w. Composition: 390 ohms ±10%, 1/4 w.	J1	4033513-P4	Contact, electrical; sim to Bead Chain L93-3.	C15 C16	5494481-P112	Ceramic disc: .001 µf ±10%, 500 VDCW; sim to RMC Type JF Discap.	CR2 CR3 and	4038056-P1	Germanium,	R32*	3R 77-P752J	Composition: 7500 ohms ±5%, 1/2 w. Deleted by REV A.	RTI	5490828-P41	Thermistor: 30 ohms ±10%, color code black,	CR4 CR5	19 Al 15 250-Pl	Silicon.	R17 R18	3R152-P103J 3R152-P622J	Composition: 10,000 ohms $\pm 5\%$, $1/4$ w. Composition: 6200 ohms $\pm 5\%$, $1/4$ w.
	[Q1 5490277-P1		Ll thru	19C311181-G3	INDUCTORS	C17	19B209243-P7 5494481-P108	Polyester: 0.1 µf ±20%, 50 VDCW. Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to	CR4 CR5 thru	19 Al 15 250-P1	Silicon.	R33*	3R 77-P912J 3R 77-P203J	Composition: 9100 ohms ±5%, 1/2 w. Earlier than REV A. Composition: 20,000 ohms ±5%, 1/2 w.	RT2	54 90 828-P9	white; sim to Globar Type Bl211H-4. Thermistor: 10,000 ohms ±10%, color code yellow; sim to Globar Type 551H8.	CR 6 CR 7	4036887-P3 19A115250-P1	Silicon, Zener. Silicon.	R19 R20	3R152-P123J 3R152-P223J	Composition: 12,000 ohms ±5%, 1/4 w. Composition: 22,000 ohms ±5%, 1/4 w.
A344		VRMS; sim to Elco 3303. RF AMPLIFIER ASSEMBLY	L3			C19 and	19B209243-P5	RMC Type JF Discap. Polyester: 0.047 µf ±20%, 50 VDCW.	CR7	19Al15250-Pl	Silicon. Added by REV A.	R34 R35	3R 77-P332K 3R 77-P330K	Composition: 3300 ohms ±10%, 1/2 w. Composition: 33 ohms ±10%, 1/2 w.	RT3*	5490828-P9	Thermistor: 10,000 ohms ±10%, color code yellow; sim to Globar Type 551H8. Added by REV. A.	CR9			R21 R22	3R152-P103J 3R152-P301J	Composition: $10,000$ ohms $\pm 5\%$, $1/4$ w. Composition: 300 ohms $\pm 5\%$, $1/4$ w.
		19B204770-G1	P1 P2	40 29 840-P2 40 29 840-P1	Contact, electrical: sim to Amp 42827-2. Contact, electrical: sim to AMP 41854.	C20 C21*	19 B2 09 243-P3	Polyester: 0.022 µf ±20%, 50 VDCW. Earlier than REV A.	J1	4033513-P4	JACKS AND RECEPTACLES	R36 R37*	3R 77-P681J 3R 77-P822J	Composition: 680 ohms ±5%, 1/2 w. Composition: 8200 ohms ±5%, 1/2 w. Deleted by REV A.	T1	19 Al 16 04 0-Pl	TRANSFORMERS	FL1	19B205280-G1	TONE FREQUENCY NETWORK 19B205280	R23 R24	3R152-P223J 3R152-P433J	Composition: 22,000 ohms ±5%, 1/4 w. Composition: 43,000 ohms ±5%, 1/4 w.
c	5494481-P14	Ceramic disc: .002 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	01	10.4115.000 m	TRANSISTORS	C22	19B209243-P1 19B209243-P116	Polyester: 0.01 µf ±20%, 50 VDCW. Polyester: 0.15 µf ±10%, 50 VDCW.	thru J22		inductors	R38*	3R77-P752J 3R77-P622J	Composition: 7500 ohms ±5%, 1/2 w. Earlier than REV A. Composition: 6200 ohms ±5%, 1/2 w.		15/11/07/0-71	Pri: 19,3 ohms ±10% DC res, Sec: 23.5 ohms ±10% DC res.		19B205280-G2 19B205280-G3 19B205280-G4	71.9 Hz 77.0 Hz 82.5 Hz 88.5 Hz	R25 R26	3R 15 2-P133J 3R 15 2-P123J	Composition: 13,000 ohms ±5%, 1/4 w. Composition: 12,000 ohms ±5%, 1/4 w.
	R1 4038056-p1	DIODES AND RECTIFIERS	Q2	19A115889-P1 19A115245-P1	Silicon, NPN.	C23 C24*	19B209243-P107 19B209243-P106	Polyester: 0.1 µf ±10%, 50 VDCW. Polyester: .068 µf ±10%, 50 VDCW. Deleted by REV A.	L1 L2	19C311181-G1 19C311181-G2	Coil. Includes tuning slug 4038368-Pl.	R39*	3R 77-P820J 3R 77-P131J	Composition: 8200 ohms ±5%, 1/2 w. Earlier than REV A.	A350		ENCODER/DECODER 4EK16A10 19C311797-G1 REV A		19 B205 280-G5 19 B205 280-G6 19 B205 280-G7 19 B205 280-G8	94.8 Hz 100.0 Hz 103.5 Hz 107.2 Hz	R27	3R 15 2-P151J 3R 15 2-P56 2J	Composition: 150 ohms ±5%, 1/4 w. Composition: 5600 ohms ±5%, 1/4 w.
		TRANSISTORS	45	19A115123-P1	Silicon, NPN; sim to Type 2N2712.	C25	54 96 267-P6	Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 150D.	L3	19 A1 27134-G1	Choke. Includes tuning slug 7486872-P7.	R40 R41*	3R 77-P241J	Composition: 130 ohms ±5%, 1/2 w. Composition: 240 ohms ±5%, 1/2 w.		19 B209 243-P1 7			19B205280-G9 19B205280-G10 19B205280-G11 19B205280-G12	110.9 Hz 114.8 Hz 118.8 Hz 123.0 Hz	R29 R30	3R152-P513J 3R152-P334J	Composition: 51,000 ohms ±5%, 1/4 w. Composition: 0.33 megohms ±5%, 1/4 w.
· ·	l 19Al15342-Pl	Silicon, NFN.	R1 and R2	3R 77-P103K	Composition: 10,000 ohms ±10%, 1/2 w.	C26*	5496267-P28 19B209243-P14	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Earlier than REV A. Polyester: 0.33 µf ±20%, 50 VDCW.	Q1 thru	19A115123-P1	TRANSISTORS	R42*	3R 77-P240J 3R 77-P300J	Composition: 24 ohms ±5%, 1/2 w. Earlier than REV A. Composition: 30 ohms ±5%, 1/2 w.	C2 and	19B209243-P205	Polyester: 0.22 µf ±20%, 50 VDCW. Polyester: 0.047 µf ±5%, 50 VDCW.		19B205280-G13 19B205280-G14 19B205280-G15 19B205280-G16	127.3 Hz 131.8 Hz 136.5 Hz 141.3 Hz	R31 R32	3R 152-P104J 3R 152-P822J	Composition: 0.1 megohms ±5%, 1/4 w. Composition: 8200 ohms ±5%, 1/4 w.
R	1 3R152-P510J	Composition: 51 ohms ±5%, 1/4 w.	R3 R4	3R 77-P512J 3R 152-P333 K	Composition: 5100 ohms ±5%, 1/2 w. Composition: 33,000 ohms ±10%, 1/4 w.	C27	5496267-P6	Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 150D.	Q6 Q7	19A115300-P4	Silicon, NPN; sim to Type 2N3053.	R42*	3R 77-P200J 3R 77-P160J	Composition: 20 ohms ±5%, 1/2 w. Earlier than REV A. Composition: 16 ohms ±5%, 1/2 w.	C4	i .	Polyester: 0.1 µf ±5%, 50 VDCW.		19B205280-G17 19B205280-G18 19B205280-G19 19B205280-G20	146.2 Hz 151.4 Hz 156.7 Hz 162.2 Hz	R33	5495948-P342	Deposited carbon: 26,700 ohms ±1%, 1/2 w; sim to Texas Instrument CD1/2MR.
т	Bl 7487424-P19	TERMINAL BOARDS Miniature, phen: 3 terminals.	R5 R6	3R152-P103J 3R77-P332K	Composition: 10,000 ohms ±5%, 1/4 w. Composition: 3300 ohms ±10%, 1/2 w.	C28*	5496267 -P2 29	Tantalum: 0.68 µf ±10%, 35 VDCW; sim to Sprague Type 150D. Deleted by REV A.	Q8 Q9	19A115123-P1 19A115362-P1	Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2925.	R44	19B209358-P103	±10%, 0.2 w; sim to CTS Type X-201. Wirewound: .27 ohms ±105%, 2 w; sim to IRC	C6	1	Polyester: 0.1 \(\mu f \pm 20\%, \) 50 VDCW. Polyester: 0.047 \(\mu f \pm 5\%, \) 50 VDCW. Polyester: 0.1 \(\mu f \pm 5\%, \) 50 VDCW.		19B205280-G21 19B205280-G22 19B205280-G23 19B205280-G24	167.9 Hz 173.8 Hz 179.9 Hz 186.2 Hz	R34 R35	5495948-P233 5495948-P365	Deposited carbon: 2150 ohms ±1%, 1/2 w; sim to Texas Instrument CDI/2MR. Deposited carbon: 46,400 ohms ±1%, 1/2 w; sim
A346		CRYSTAL FILTER 19B204616-G3	R7 R8	3R 77-P123K 3R 77-P622J	Composition: 12,000 ohms ±10%, 1/2 w. Composition: '6200 ohms ±5%, 1/2 w.	C29*	5496267-P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Deleted by REV A.	Q10	19A115123-P1	Silicon, NPN; sim to Type 2N2712.	R45 R46	3R 77-P123J 3R 77-P913J	Type BWH. Composition: 12,000 ohms ±5%, 1/2 w. Composition: 91,000 ohms ±5%, 1/2 w.	C8	1	Polyester: 0.047 µf ±5%, 50 VDCW.		19B205280-G25 19B205280-G26	192.8 Hz 203.5 Hz	R36	5495948-P301	to Texas Instrument CD1/2MR. Deposited carbon: 10,000 ohms ±1%, 1/2 w; sim to Texas Instrument CD1/2MR.
F	L5 19B206692-G1	FILTERS	R9 R10	3R 77-P302J 3R 77-P202J	Composition: 3000 ohms ±5%, 1/2 w. Composition: 2000 ohms ±5%, 1/2 w.	C30	19B209243-P16 19B209243-P102	1	R1 R2	3R 77-P102K 3R 77-P153J	Composition: 1000 ohms ±10%, 1/2 w. Composition: 15,000 ohms ±5%, 1/2 w.	R48*	3R 77-P30 2J 3R 77-P33 2J	Composition: 3000 ohms ±5%, 1/2 w. Earlier than REV A.	C10	19B209243-P207 19B209243-P112	Polyester: 0.22 µf ±20%, 50 VDCW. Polyester: 0.1 µf ±5%, 50 VDCW. Polyester: 0.22 µf ±10%, 250 VDCW.	J1 thru	4033513-P4	JACKS AND RECEPTACLES	R37	5495948-P65	Deposited carbon: 46.4 ohms ±1%, 1/2 w; sim to Texas Instrument CD1/2MR.
		RESISTORS	R11	3R77-P201J	Composition: 200 ohms ±5%, 1/2 w.	C32 C33	19B209243-P7 19B209243-P17	Polyester: 0.1 μf ±20%, 50 VDCW. Polyester: 0.22 μf ±20%, 50 VDCW.	R3 R4	3R 77-P823K 3R 77-P472K	Composition: 82,000 ohms ±10%, 1/2 w. Composition: 4700 ohms ±10%, 1/2 w.	R49 R50	3R 77-P103J 3R 77-P22 2J	Composition: 3300 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±5%, 1/2 w. Composition: 2200 ohms ±5%, 1/2 w.	C12 C13	19B209243-P207 19B209243-P17	Polyester: 0.22 µf ±10%, 250 VDCW. Polyester: 0.1 µf ±5%, 50 VDCW. Polyester: 0.22 µf ±20%, 50 VDCW.	,,	104315555	INDUCTORS	R38	3R 15 2-P204J 54 95 94 8-P3 85	Composition: 0.2 megohms ±5%, 1/4 w. Deposited carbon: 75,000 ohms ±1%, 1/2 w; sim to Texas Instrument CD1/2MR.
R R		Composition: 5600 ohms ±10%, 1/4 w. Composition: 10,000 ohms ±10%, 1/4 w.	Tl			C34 C35	4029003-P207 19B209243-P5	Silver mica: 1830 pf ±2%, 500 VDCW; sim to Electro Motive Type DM-20. Polyester: 0.047 µf ±20%, 50 VDCW.	R5 R6	3R77-P102K 3R77-P153J	Composition: 1000 ohms ±10%, 1/2 w. Composition: 15,000 ohms ±5%, 1/2 w.	R51 R52	3R 77-P103J 3R 77-P682J	Composition: 2200 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±5%, 1/2 w. Composition: 6800 ohms ±5%, 1/2 w.	C14 C15	19B209243-P7 19B209243-P7 5496267-P1	Polyester: 0.22 µ1 ±20%, 50 VDCW. Polyester: 0.1 µf ±20%, 50 VDCW. Tantalum: 6.8 µf ±20%, 6 VDCW; sim to		19A115690-P1	Coil, RF: 880 MH ±5%, sim to Artted AC5672.	R40	5495948-P329	Deposited carbon: 19,000 ohms ±1%, 1/2 w; sim Texas Instrument CD1/2MR.
A347		SECOND MIXER 19B216119-G1 REV A	CI	19C301540-P261		C36	19B209243-P7 5496267-P28	Polyester: 0.047 µf 120%, 50 VDCW. Tantalum: 0.47 µf ±20%, 35 VDCW; sim to	R7 R8	3R 77-P823K 3R 77-P472K	Composition: 82,000 ohms ±10%, 1/2 w. Composition: 4700 ohms ±10%, 1/2 w.	R53*	3R 77-P473J 3R 77-P303J	Composition: 47,000 ohms ±5%, 1/2 w. Earlier than REV A. Composition: 30,000 ohms ±5%, 1/2 w.	C16	19 B209 243-P5	Sprague Type 150D. Polyester: 0.047 µf ±20%, 50 VDCW.	Q1 Q2	19 A1 15123-P1 19 A1 15362-P1	Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2925.	R41 R42	5495948-P285 5495948-P412	Deposited carbon: 7500 ohms ±1%, 1/2 w; sim to Texas Instrument CD1/2MR. Deposited carbon: 130,000 ohms ±1%, 1/2 w; sim
				5491798-P3	-80 PPM. Tuning slug.		5496267-P17	Sprague Type 150D. Earlier than REV A. Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D.	R9	3R 77-P10 2K	Composition: 1000 ohms ±10%, 1/2 w.	R54	3R 77-P822J	Composition: 8200 ohms ±5%, 1/2 w.	C17	5496267-P417	Tantalum: 1.0 µf ±5%, 35 VDCW; sim to Sprague Type 150D.	Q3 and Q4	19Al 15123-Pl	Silicon, NPN; sim to Type 2N2712.			to Texas Instrument CDI/2MR.
0	1	(Part of T1).	¥1	19A110192-P3				-5-25- 1/be 7000'															
					Toposacuse range -50 C to +13 C.																		

VOLTAGE READINGS VOLTAGE READINGS ARE TYPICAL READINGS VOLTAGE READINGS ARE TIPICAL READINGS MEASURED TO SYSTEM NEGATIVE (J442-8) WITH TEST SET MODEL 4EX3A10 OR A

SENO SIGNAL IN WITH SQUELCH CONTROL FULLY COUNTERCLOCKWISE (MAXIMUM SQUELCH) US = SQUELCH CONTROL FULLY CLOCKWISE WITH A ONE MILLIVOLT MODULATED SIGNAL (UNSQUELCHED) AND 5 WATT AUDIO OUTPUT

MODEL NO. FREQ. RANGE FREQ. GUARD ### 4ER39C28 25 - 33 MHZ 1

4ER39C29 33 - 42 MHZ 1

4ER39C30 42 - 50 MHZ 1

4ER39C31 25 - 33 MHZ 2

4ER39C32 33 - 42 MHZ 2

4ER39C33 42 - 50 MHZ 2

4ER39C33 42 - 50 MHZ 2

4ER39C34 25 - 33 MHZ 4

4ER39C36 42 - 50 MHZ 4

4ER39C36 42 - 50 MHZ 4

4ER39C36 42 - 50 MHZ 4

4ER39C37 25 - 33 MHZ 4

4ER39C37 25 - 33 MHZ 4 4ER39C42 42-50 MHZ 2 X 4ER39C43 25-33 MHZ 4 X 4ER39C44 33-42 MHZ 4 X 4ER39C45 42-50 MHZ 4 X REV. LTR. BLOCK PL19E500873G4 PL19E500873G5 PL19E500873G6

● LOW SPLIT 25-33 MHZ

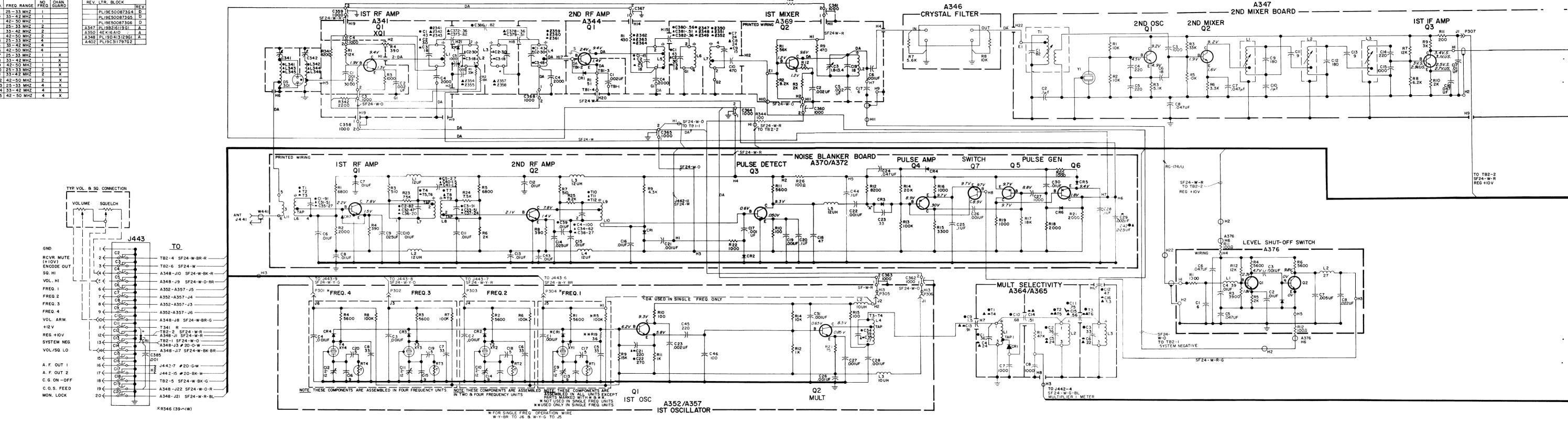
▲ MID SPLIT 33-42 MHZ ■ HIGH SPLIT 42-50 MHZ

■ VALUE OF R47 IS DETERMINED BY TEST (SEE TEST SPEC. 19A127182).

THESE ARE ONLY PARTS PRESENT ON

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

ALL RESISTORS ARE 1/2 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K-1000 OHMS OR MEG = 1,000,000 OHMS CAPACITOR VALUES IN PIOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWE BY UF = MICROFARADS, INDUCTANCE VALUES IN MICROFIENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H= HENRYS.

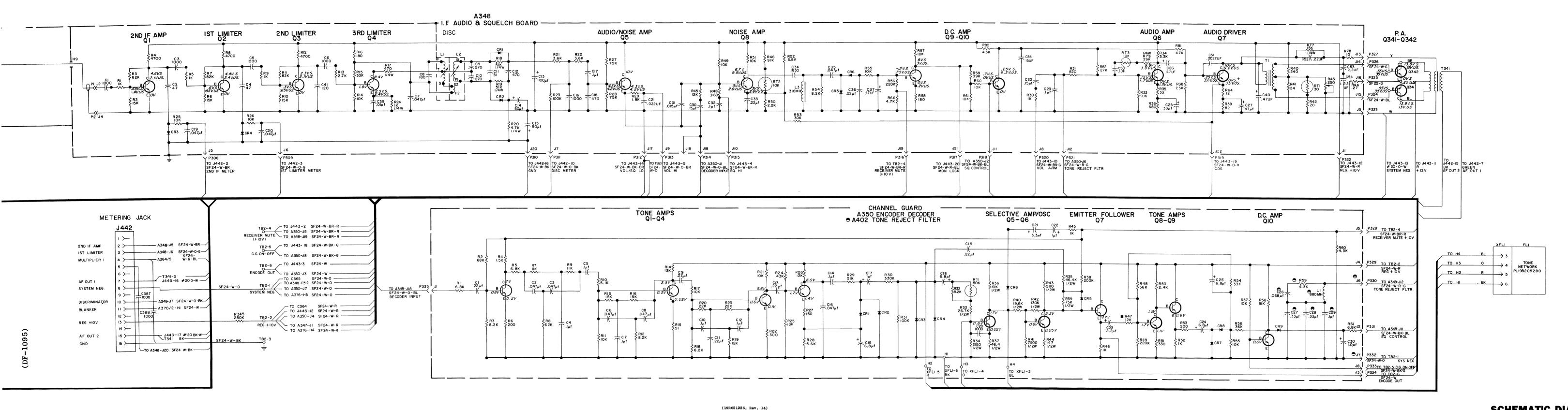


SCHEMATIC DIAGRAM

25—50 MHZ MASTR RECEIVER MODELS 4ER39C28-45

(19R621226, Rev. 11)

Issue 3



SCHEMATIC DIAGRAM

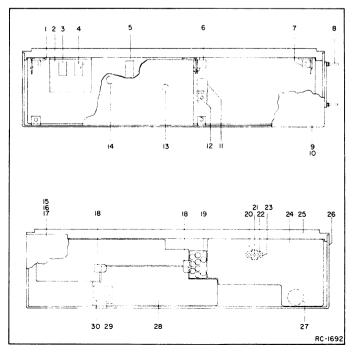
25—50 MHZ MASTR RECEIVER MODELS 4ER39C28-45

Г	BOL GE PART NO.	DESCRIPTION	SYMBO	I GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	CAMBUI	GE PART NO.	DESCRIPTION
318	DUL GL FART NU.	JEGGIII HOI	31,111001	GE I FILL ING.					311111111	GE I ART 110.		SIMDUL	UL FAILI NO.	DECOMM 11011	J J WIDOL	-		- STWIDOL	UL I ART NO.	SECONII HON	SIMBUL	GL FART NU.	DESORII HOR
1	12 3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.	R55	1	Composition: 10,000 ohms ±5%, 1/2 w.			RESISTORS	C9	5491601P123	Phenolic: 1.5 pf ±5%, 500 VDCW.	C9	7491827P3	Ceramic disc: .025 µf +80% -20%, 50 VDCW; sim to Sprague Type 29C.	R5	3R152P682K	Composition: 6800 ohms ±10%, 1/4 w.	T7		COIL ASSEMBLY T7 19B204696G1	1.1		INDUCTORS
	13 3R77P153J 14 3R77P133J	Composition: 15,000 ohms ±5%, 1/2 w.	R56		Composition: 36,000 ohms ±5%, 1/2 w.	R1 thru	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	C10	5491601P117 5491601P118	Phenolic: 0.68 pf ±5%, 500 VDCW.	C12	7491827P2	Ceramic disc: .01 µf +80% -30%, 50 VDCW;	R6	3R152P202J 3R152P511J	Composition: 2000 ohms ±5%, 1/4 w. Composition: 510 ohms ±5%, 1/4 w.	Т9		T8 19B204696G2 T9 19B204696G3	LI	19C307007P3	Coil, RF: 39 μh $\pm 10\%$, 1.8 ohms DC res max; sim to Delevan 1537-727.
	14 3R77P133J 15 3R77P510J	Composition: 13,000 ohms ±5%, 1/2 w. Composition: 51 ohms ±5%, 1/2 w.	R57		Composition: 10,000 ohms ±10%, 1/2 w. Composition: 91,000 ohms ±5%, 1/2 w.	R5	3R152P104K	Composition: 0.1 megohm ±10%, 1/4 w.	C11	5491601P118 5491601P132	Phenolic: 0.75 pf ±5%, 500 VDCW. Phenolic: 4.7 pf ±5%, 500 VDCW.	C13		sim to Sprague Type 19C.	R8	3R152P391K	Composition: 390 ohms ±10%, 1/4 w.				L2	7488079P48	Choke, RF: 27 µh ±10%, 1.40 ohms DC res max; sim to Jeffers 4422-9K.
i	16 3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.	R59*		Composition: 1800 ohms ±5%, 1/2 w.	thru R8			C13	5491601P137	Phenolic: 0.91 pf ±5%, 500 VDCW.	C14	7491827P3	Ceramic disc: .025 µf +80% -20%, 50 VDCW; sim to Sprague Type 29C.	R9	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.	СЗ	5496218P62	Ceramic disc: 91 pf ±5%, 500 VDCW, temp			
1	17 3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.		ļ	In REV C and earlier:	R9	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	C14	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW.	C17	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.		1000015000	coef 0 PPM.	01	19A115245P1	
	18 3R77P622J	Composition: 6200 ohms ±5%, 1/2 w.		3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.	R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	C15	5491601P115	Phenolic: 0.56 pf ±5%, 500 VDCW.	C18	5496219 P 55	RMC Type JF Discap. Ceramic disc: 47 pf ±5%, 500 VDCW, temp coef	R11	3R152P562K	Composition: 5600 ohms ±10%, 1/4 w.		1 19B209170P2	Ceramic disc: .01 µf +80% -30%, 50 VDCW; sim to Sprague Type 19C.	Q2	19A115123P1	Silicon, NPN; sim to Type 2N2712.
	19 3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.	R60		Composition: 4300 ohms ±5%, 1/2 w.	R11 and	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	C16	5491601P130	Phenolic: 3.3 pf ±5%, 500 VDCW.			0 РРМ.	R12	3R152P822K 3R152P104K	Composition: 8200 ohms ±10%, 1/4 w.	C3:	3 5496218P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM.			
1	20 3R77P223J 21 3R77P103J	Composition: 22,000 ohms ±5%, 1/2 w.	R61	3R77P682K	Composition: 6800 ohms ±10%, 1/2 w.	R12	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.		İ	DIODES AND RECTIFIERS	C19	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R14	3R152P104K 3R152P203J	Composition: 0.1 megohms ±10%, 1/4 w. Composition: 20,000 ohms ±5%, 1/4 w.	C3	7 5496218P48	Ceramic_disc: 24 pf ±5%, 500 VDCW, temp	R1	3R152P102K	
1	21 3R77P103J 22 3R77P301J	Composition: 10,000 ohms ±5%, 1/2 w. Composition: 300 ohms ±5%, 1/2 w.				R15		Composition: 100 ohms ±10%, 1/4 w.	CR1	4038056P1	Germanium.	C20	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	R15	3R152P332K	Composition: 3300 ohms ±10%, 1/4 w.		1	coef 0 PPM.	R2	3R152P123K	Composition: 12,000 ohms ±10%, 1/4 w.
	23 3R77P223J	Composition: 22,000 ohms ±5%, 1/2 w.	RT1	5490828P22	Thermistor: 50,000 ohms ±10%, color code yellow; sim to Globar Type 763H,	R19	3R152P360J	Composition: 36 ohms ±5%, 1/4 w.			RESISTORS	C21 and	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R16	3R152P102K	Composition: 1000 ohms ±10%, 1/4 w.		1		R3	3R152P392K	Composition: 3900 ohms ±10%, 1/4 w.
1	24 3R77P433J	Composition: 43,000 ohms ±5%, 1/2 w.				R21	3R152P750J	Composition: 75 ohms ±5%, 1/4 w.	R1	3R152P473K	Composition: 47,000 ohms ±10%, 1/4 w.	C22	5496219P51		R17	3R152P183K	Composition: 18,000 ohms ±10%, 1/4 w.	L8	19A121395P1	Coil.	R4	3R152P562K	Composition: 5600 ohms ±10%, 1/4 w.
1	25 3R77P133J	Composition: 13,000 ohms ±5%, 1/2 w.	XFL1	1 19A121920G3	Pood migrafilled phane 7 nine mated at 1 am at						TRANSFORMERS	C23*	5496219P51	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef 0 PPM.	R18	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.			RESISTORS	R5	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.
1	26 3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.	AFL!	19812192003	Reed, mica-filled phen: 7 pins rated at 1 amp at 500 VRMS with 4-1/2 inches of cable.	RT1	19B209284P5	Disc: 43 ohms res nominal at 25°C, color code	T1	19B205325G2	Coil, includes tuning slug 5491798P4.			In Models earlier than REV A:	R19 and	3R152P102K	Composition: 1000 ohms ±10%, 1/4 w.	R2	3R152P752J	Composition: 7500 ohms ±5%, 1/4 w.	R6	3R152P562K	Composition: 5600 ohms ±10%, 1/4 w.
	27 3R77P151J	Composition: 150 ohms ±5%, 1/2 w.	A352		FIRST OSCILLATOR ASSEMBLY	thru RT4		green.	Т2	19B205325G1	Coil, includes tuning slug 5491798P4.		5496219P44	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef 0 PPM.	R20	3R152P202J			5491798P4	Tuning slug. (Used in T7 and T8).	R11* and R12*	3R152P101K	Composition: 100 ohms ±10%, 1/4 w. Added by REV B.
1	28 3R77P562J 29 3R77P513J	Composition: 5600 ohms ±5%, 1/2 w.	thru A357		A352 19B204419G13 (4ER39C28, 37) A353 19B204419G16 (4ER39C31, 40)			TRANSFORMERS	and T3			C24	19A116080P5	Polyester: .047 µf ±20%, 50 VDCW.	R21	3R152P202J 3R152P102K	Composition: 2000 ohms ±5%, 1/4 w. Composition: 1000 ohms ±10%, 1/4 w.	T10	5491798P5	Tuning slug. (Used in T9).	R12+		
į	30 3R77P334J	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 0.33 megohm ±5%, 1/2 w.			A354 19B204419G14 (4ER39C34, 43) A355 19B204419G17 (4ER39C39, 30, 38, 39) A356 19B204419G15 (4ER39C32, 33, 41, 42)	T3 and		COIL ASSEMBLY T3 19B205416G1	T4	19B205325G2	Coil, includes tuning slug 5491798P4.	C25	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	R26*	3R152P101K	Composition: 100 ohms ±10%, 1/4 w. Added by	thru		COIL ASSEMBLY T10 19B204697G1 T11 19B204697G2	A402		TONE REJECT FILTER 19C311797G2
	31 3R77P104J	Composition: 0.1 megohms ±5%, 1/2 w.			A357 19B204419G18 (4ER39C35, 36, 44, 45)	T4		T4 19B205416G2	T5 and	19B205325G1	Coil, includes tuning slug 5491798P4.	C26	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.		1	REV B.		1 :	T11 198204697G2 T12 198204697G3			
	32 3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.						CAPACITORS	Т6			C27	4029003P8	Silver mica: 1000 pf ±5%, 500 VDCW; sim to					j		C26	19A116080P206	
1	33 19A116278P342	Metal film: 26,700 ohms ±2%, 1/2 w.	C1	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C34	4 5496218P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.	A369		FIRST MIXER ASSEMBLY 198204430G6	C28	19A116080P7	Electro Motive Type DM-20. Polyester: 0.1 µf ±20%, 50 VDCW.	T1 thru		COIL ASSEMBLY Tl 198204694Gl	C4	5496218P63	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef 0 PPM.	C27	19A116080P210	Polyester: 0.000 µf ±10%, 50 VDCW.
1	34 19A116278P233	Metal film: 2150 ohms ±2%, 1/2 w.	thru C4	•	and type or biscap.	C35	5 5496218P249	Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef				C29	1	Ceramic disc: .002 pf ±10%, 1000 VDCW; sim to	Т3		T2 19B204694G2 T3 19B204694G3	C1	19B209170P2	Ceramic disc: .01 µf +80% -30%, 50 VDCW;	and C28		
ŀ	35 19A116278P365	Metal film: 46,400 ohms ±2%, 1/2 w.	C5 thru C8	5496219P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.			-80 PPM.			CAPACITORS			RMC Type JF Discap.			0.0.075000	and C16	1	sim to Sprague Type 19C.	C29*	19A116080P205	Polyester: 0.047 µf ±10%, 50 VDCW.
1	36 19A116278P301 37 19A116278P65	Metal film: 10,000 ohms ±2%, 1/2 w. Metal film: 46.4 ohms ±2%, 1/2 w.	C8 C9	5491271P106	W-4-1-1			INDUCTORS	C2	5494481P114	Ceramic disc: .002 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C30	19A116080P1 19A116080P1	Polyester: .01 µf ±20%, 50 VDCW. Polyester: .01 µf ±20%, 50 VDCW.	C1	5496218P62		C34	5496218958	Ceramic disc: 62 pf ±5%, 500 VDCW, temp			Earlier than REV A:
1	38 3R77P204J	Composition: 0.2 megohm ±5%, 1/2 w.	thru Cl2		Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.	L4	19A121464P2	Coil, Includes:	СЗ	5491271P106	Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.	C40	5491601P23	Phenolic: 1.5 pf ±10%, 500 VDCW.			coef 0 PPM.	ca	5496218P49	coef 0 PPM. Ceramic disc: 27 pf ±5%, 500 VDCW, temp		19B209243P107	Polyester: 0.1 µf ±10%, 50 VDCW.
	39 5495948P385	Deposited carbon: 75.000 ohms ±1%, 1/2 w: sim	C13	5496219P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp		5491798P5	Tuning slug.	C5	5494481P114	Ceramic disc: .002 pf ±10%, 1000 VDCW; sim to	C41	5491601P22	Phenolic: 1.2 pf ±10%, 500 VDCW.	C6	19B209170P2	Ceramic disc: .01 µf +80% -30%, 50 VDCW; sim to Sprague Type 19C.			coef 0 PPM.			JACKS AND RECEPTACLES
	10.1116050500	to Texas Instrument CD1/2MR.	thru C16	1	coef 0 PPM.			SOCKETS	C6	5494481P12	RMC Type JF Discap.	C42	5494481P116	Ceramic disc: .003 pf ±10%, 1000 VDCW; sim to	C31	5496218P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp			INDUCTORS	J6	4033513P4	Contact, electrical; sim to Bead Chain L93-3.
	40 19A116278P329 41 19A116278P285	Metal film: 19,600 ohms ±2%, 1/2 w. Metal film: 7500 ohms ±2%, 1/2 w.	C17	19C300685P93	Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coef	XY1 thru		Refer to Mechanical Parts (RC-1692).	"	5494481P12	Ceramic disc: .001 pf \pm 10%, 1000 VDCW; sim to RMC Type JF Discap.	C43	7491827P2	RMC Type JF Discap. Ceramic disc: .01 µf +80% -30%, 50 VDCW;	C35	5496218P49	Ceramic disc: 27 pf ±5%, 500 VDCW, temp	L9	19A121396P1	Coil.	J7		
	42 19A116278P412	Metal film: 130,000 ohms ±2%, 1/2 w.	thru C20	1	• • • • • • • • • • • • • • • • • • •	XY4			C17	5496218P237	Ceramic disc: 6 pf ±5%, 500 VDCW, temp coef -80 PPM.			sim to Sprague Type 19C.			coef 0 PPM.	L10	4029250P15	Coil.			INDUCTORS
	43 19A116278P269	Metal film: 5110 ohms ±2%, 1/2 w.	C21	5496219P771	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -750 PPM.			When recordering give CF Part No. and specify	C19	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef	C44*	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW. Added by REV B.	11		INDUCTORS	-	:	RESISTORS	L1	19A115690P1	Coil, RF: 880 mh ±5%, sim to Artted AC5672.
1	44 19A116278P117	Metal film: 147 ohms ±2%, 1/2 w.	C22	5496219P773	Ceramic disc: 270 pf ±5%, 500 VDCW, temp coef			When reordering give GE Part No. and specify exact freq needed.			-80 PPM.			DIODES AND RECTIFIERS	L6	19A121393P1	Coil.	R25	3R152P822K	Composition: 8200 ohms ±10%, 1/4 w.			RESISTORS
1	45 3R77P102J	Composition: 1000 ohms ±5%, 1/2 w.	C23	5494481P114	Ceramic disc: .002 pf ±10%, 1000 VDCW; sim to			25-42 MHz crystal freq = (OF +5.30 MHz) : 3.			TERMINALS	CR1	1	Silicon.	L11	4039250P15	Coil.		5491798P5	Tuning slug. (Used in Tl2).	R59*	3R77P182J	Composition: 1800 ohms ±5%, 1/2 w.
1	46				RMC Type JF Discap.	Y1	19B206576P1	42-50 MHz crystal freq = (0F -5.30 MHz) ÷ 3,	E1	4038104P1	Lug: solder dipped brass.	CR2 thru	4038056P1	Germanium.		5491798P4 5491798P5	Tuning slug. (Used in Tl and T2).		5491798P4	Tuning slug. (Used in TlO and Tll).		3R152P432J	In REV A and earlier:
		The value of Resistor R47 must be obtained from	C26 thru		Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	thru Y4	198206576P1	Quartz: freq range 10086.666 to 12766.666 KHz, temp range -30°C to +85°C. (25-33 MHz).			INDUCTORS	CR4	19A115250P1	Silicon.	T4	5491798P5	Tuning slug. (Used in T3). COIL ASSEMBLY	A376	Shrine in hills	LEVEL SHUT-OFF SWITCH		3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.
		the component, then find corresponding value in parts list for the correct part number.	C28	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to	Y1	19B206576P2	Quartz: freq range 12766.667 to 15766.666 KHz,	L2	19A121082G2	Toroidal coil.	CR6	1	Germanium.	thru T6		T4 19B204695G1 T5 19B204695G2		e Chinama	19C303985G1		l	CHASSIS AND RF ASSEMBLY 19E500873 G4-6
	47A 3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.			RMC Type JF Discap.	thru Y4		temp range -30°C to +85°C. (33-42 MHz).			TRANSISTORS	and CR7					T6 19B204695G3			CAPACITORS			REV E
	47B 3R77P912J	Composition: 9100 ohms ±5%, 1/2 w.	C45	- 1	Silver mica: 220 pf ±5%, 500 VDCW.	Y1	19B206576P3	Quartz: freq range 12233.333 to 16233.333 KHz, temp range -30°C to +85°C. (42-54 MHz).	Q2	19A115245P1	Silicon, NPN.		1	INDUCTORS		İ		C1	5496219P237	Ceramic disc: 6.0 pf ±5%, 500 VDCW, temp coef -80 PPM.			
- 1	47C 3R77P103J 47D 3R77P113J	Composition: 10,000 ohms ±5%, 1/2 w. Composition: 11,000 ohms ±5%, 1/2 w.	C46	5496219 P 563	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef -330 PPM.	Y4					RESISTORS	L1 thru	7488079P17	RF: 12 μh ±10%, sim to Jeffers Type 44.	C2	5496218P61	Ceramic disc: 82 pf ±5%, 500 VDCW, temp coef 0 PPM.	C2	19B209243P1	Polyester: .01 µf ±20%, 50 VDCW.	C358 thru C365	5493392P7	Ceramic feed-thru: .001 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.
1	47E 3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.			DIODES AND RECTIFIERS	A364		MULTIPLIER SELECTIVITY ASSEMBLY	R1	3R152P563J	Composition: 56,000 ohms ±5%, 1/4 w.	L5			C10	19B209170P2	Ceramic disc: .01 µf +80% -30%, 50 VDCW;	C3	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	1 1		
	47F 3R77P133J	Composition: 13,000 ohms ±5%, 1/2 w.	CR1		Silicon.	and A365		A364 19B205326G1 (4ER39C28, 31, 34, 37, 40, 43) A365 19B205326G2 (4ER39C29, 30, 32, 33, 35, 36, 38, 39, 41, 42, 44, 45)	R2	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.		10411504001	TRANSISTORS	(33	5496218P55	sim to Sprague Type 19C. Ceramic disc: 47 pf ±5%, 500 VDCW, temp	C4	7491827 P 2	Ceramic disc: .01 µf +80% -30%, 50 VDCW;	C367 and C368	5493392P7	Ceramic feed-thru: .001 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.
	47G 3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.	thru CR4	u					R3	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.	Q1 thru Q3	19A115342P1	Silicon, NPN.			coef 0 PPM.	C5*	19B209243P5	sim to Sprague Type 19C. Polyester: .047 uf ±20%. 50 VDCW.	C372	5491601P110	Phenolic: 0.36 pf ±5%, 500 VDCW.
1	47H 3R77P752J	Composition: 7500 ohms ±5%, 1/2 w.			JACKS AND RECEPTACLES				R9	1	Composition: 470 ohms ±10%, 1/4 w.	Q4 Q4	19Al15768Pl	Silicon, PNP.	C36	5496218P46	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef 0 PPM.	and C6*	19820924389	Foljester: .047 µ1 120%, 30 YDCW.	C373	5491601P116	Phenolic: 0.62 pf ±5%, 500 VDCW.
	48 3R77P563J	Composition: 56,000 ohms ±5%, 1/2 w.	J1 thru J6		Contact, electrical: sim to Bead Chain L93-3.	C1 and	5496218P252	Ceramic disc: 36 pf ±5%, 500 VDCW, temp coef -80 PPM.	R12	3R152P750J	Composition: 75 ohms ±5%, 1/4 w.	Q5	19A115706P1	Silicon, PNP.						In Models of REV A and earlier:	C378	5491601P110	Phenolic: 0.36 pf ±5%, 500 VDCW.
	3R77P224J 50 3R77P242J	Composition: 0.22 megohm ±5%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w.	16		inductors	C2 C3	5496218P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef	A370	1	NOISE BLANKER	thru Q7			1.7	19A121394P1			7491827P2	Ceramic disc: .01 µf +80% -30%, 50 VDCW; sim to Sprague Type 19C.	C379	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW.
	3877P242J 3877P331J	Composition: 330 ohms ±5%, 1/2 w.	L2	7488079P16	Choke. RF: 10 µh ±10% ind at 640 ma, 0,6 ohm			-80 PPM.	thru A372		A370 19C303540G1 (4ER39C28, 31, 34, 37, 40, 43) A371 19C303540G2 (4ER39C29, 32, 35, 38, 41, 44) A372 19C303540G3 (4ER39C30, 33, 36, 39, 42, 45)			RESISTORS				C7	7774750P11	Ceramic disc: .005 µf +100% -0%, 500 VDCW.	C380	5491601P115	Phenolic: 0.56 pf ±5%, 500 VDCW.
1	52 3R77P102J	Composition: 1000 ohms ±5%, 1/2 w.	and L3		DC res; sim to Jeffers 4421-7K.	C4 and	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.				R1	1	Composition: 6800 ohms ±10%, 1/4 w.		00150005	RESISTORS	C8	19B209243P3	Polyester: .022 µf ±20%, 50 VDCW.	C381	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW.
	3R77P201J	Composition: 200 ohms ±5%, 1/2 w.			TRANSISTORS	C5 C6	5496218P247	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef		E401C01700		R2	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w. Composition: 510 ohms ±5%, 1/4 w.	R23	3R152P752K 5491798P4	Composition: 7500 ohms ±10%, 1/4 w. Tuning slug. (Used in T4 and T5).		1	DIODES AND RECTIFIERS	C382 C385	5491601P110 7774750P4	Phenolic: 0.36 pf ±5%, 500 VDCW. Ceramic disc: .001 µf +100% -0%, 500 VDCW.
	3R77P333J	Composition: 33,000 ohms ±5%, 1/2 w.	_{Q1}	19A115330P1	Silicon, NPN,			-80 PPM.	C5	5491601P28 7491827P2	Phenolic: 2.7 pf ±10%, 500 VDCW. Ceramic disc: .01 µf +80% -30%, 50 VDCW;	R3 R4	1	Composition: 510 ohms 15%, 1/4 w. Composition: 390 ohms ±10%, 1/4 w.		5491798P4 5491798P5	Tuning slug. (Used in T6).	CR1	4038056Pl	Germanium.	C386	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
			and O2	13811333091		C7 and	5493392P107	Ceramic, stand off: .001 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type SS5D.	and C8	1.29102182	sim to Sprague Type 19C.										C387	5494481P12	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to
1						C8										İ					and C388		RMC Type JF Discap.
																							DIODES AND RECTIFIERS
16										1											CR1	19A116062P2	Selenium, Thyrector.
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SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
		JACKS AND RECEPTACLES	C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef	
J442	19B205689G2	Connector: 18 contacts.			-80 PPM.	Z357 and Z358
J443	19C303426G1	Connector: 20 pin contacts.	C3	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	
		INDUCTORS	C4	5494481P14	Ceramic disc: .002 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C2
L341 thru L346		COIL ASSEMBLY L341 19B204820G5, L342 19B204820G6 L343 19B204820G1, L344 19B204820G2 L345 19B204820G3, L346 19B204820G4		5491798Pl	MISCELLANEOUS Tuning slug. (Used in Z341).	сз
				5491798 P4	Tuning slug. (Used in Z342).	
C341	19B209159P3	Variable, subminiature: approx 1.70-6.9 pf,		5491798P5	Tuning slug. (Used in Z343).	
and C342		750 v peak; sim to EF Johnson 189.	Z347		COIL ASSEMBLY	
DS301	19B209067P1	INDICATING DEVICES Lamp, glow: 0.3 ma; sim to GE NE-2T.	thru 2349		2347 19B204767G1 2348 19B204767G2 2349 19B204767G3	Z359 thru Z361
					CAPACITORS	
P301	4029840P2	Contact, electrical; sim to Amp 42827-2.	C1	5496218P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.	
thru P313		,	C2	5496218 P25 0	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef	C1
P315 thru	4029840P2	Contact, electrical; sim to Amp 42827-2.	СЗ	5496218P245	-80 PPM.	C2
P317	400094070			3450216P243	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	сз
P319 and P320	4029840P2	Contact, electrical; sim to Amp 42827-2.			MISCELLANEOUS	C4
P322	4029840P2	Contact, electrical; sim to Amp 42827-2.		5491798P1	Tuning slug. (Used in Z347).	
P323	4029840P1	Contact, electrical: sim to AMP 41854.		5491798P4	Tuning slug. (Used in Z348).	
P324	4029840P2	Contact, electrical; sim to Amp 42827-2.		5491798 P 5	Tuning slug. (Used in Z349).	
P325	4029840P1	Contact, electrical: sim to AMP 41854.	Z350		COIL ASSEMBLY	1
P326	4029840P2	Contact, electrical; sim to Amp 42827-2.	thru Z352		Z350 19B204784G4 Z351 19B204784G5	
P327	4029840Pl	Contact, electrical: sim to AMP 41854.			Z352 19B204784G6	Z362 thru
		TRANSISTORS			CAPACITORS	Z 364
Q341* and	19A116203P2	Silicon, NPN.	C7 and C8	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.	
Q342*		Earlier than REV D:	C9	5496218P244	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef	Cl
	19A115948P1	Silicon, NPN.	C10	5494481 P 7	-80 PPM. Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to	C2
		RESISTORS		010110111	RMC Type JF Discap.	СЗ
R341	3R152P822K	Composition: 8200 ohms ±10%, 1/4 w.			MISCELLANEOUS	C3
R342	3R152P222K	Composition: 2200 ohms ±10%, 1/4 w.		5491798P1	Tuning slug. (Used in Z350).	C4
R343 and	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.		5491798P4	Tuning slug. (Used in Z351).	
R344				5491798 P 5	Tuning slug. (Used in Z352).	
R345	19A116278P444	Metal film: 0.28 megohm $\pm 2\%$, $1/2$ w.	Z354 and		COIL ASSEMBLY 2354 19B204767G4	R1
R346*	3R78P390K	Composition: 39 ohms ±10%, 1 w. Added by REV D.	2355		Z355 19B204767G5	
		TRANSFORMERS			CAPACITORS	i i
T341	19A116041P1	Audio freq: 300 to 4000 Hz, Pri: 1.00 ohms ±15% DC res,	C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	
		Sec 1: .23 ohm ±10% DC res, Sec 2: 10.5 ohms ±15% DC res.	СЗ	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	
		TERMINAL BOARDS	C4	5494481P12	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to	
TB1	7487424P26	Miniature, phen: 6 terminals.	and C5		RMC Type JF Discap.	
		CABLES			DJODES AND RECTIFIERS	
W441	19B205634G2	Coaxial: approx 5 inches long.	CR1	7777146P3	Germanium.	P314
		TUNED CIRCUITS			RESISTORS	P318
Z341		COIL ASSEMBLY	Rl	3R152P333K	Composition: 33,000 ohms ±10%, 1/4 w.	P321
thru Z343		Z341 19B204786G1 Z342 19B204786G2	R2	3R152P183K	Composition: 18,000 ohms ±10%, 1/4 w.	P328
		Z343 19B204786G3			MISCELLANEOUS	thru P335
		CAPACITORS		5491798 P 4	Tuning slug. (Used in Z354).	
C1	5496218P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.		5491798 P 5	Tuning slug. (Used in Z355).	
				:		
					·	

Z357 and Z358		1
		COIL ASSEMBLY 2357 198204783G2 2358 198204783G3
l l		
C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
сз	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
		MISCELLANEOUS
	5491798P4	Tuning slug. (Used in Z357).
ĺ	5491798P5	Tuning slug. (Used in Z358).
Z359 thru Z361		COIL ASSEMBLY Z359 19B204785G1 Z360 19B204785G2 Z361 19B204785G3
		CAPACITORS
C1	5496218P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.
C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
СЗ	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
C4	5494481P14	Ceramic disc: .002 pf ±10%, 10000 VDCW; sim to RMC Type JF Discap.
		MISCELLANEOUS
	5491798P1	Tuning slug. (Used in Z359).
	5491798P4	Tuning slug. (Used in Z360).
	5491798P5	Tuning slug. (Used in Z361).
Z362 thru Z364		COIL ASSEMBLY 2362 198204787G1 2363 198204787G2 2364 198204787G3
63	5 4 0 6 0 1 0 D 0 5 4	
Cl	5496218P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.
C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
СЗ	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
C4	5494481P14	Ceramic disc: .002 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
		RESISTORS
R1	3R152P431J	Composition: 430 ohms ±5%, 1/4 w.
		MISCELLANEOUS
	5491798P1	Tuning slug. (Used in Z362).
	5491798P4	Tuning slug, (Used in Z363),
	5491798P5	Tuning slug. (Used in Z364).
		CHANNEL GUARD MODIFICATION KIT 19A127178G1 (Used with A350)
		MISCELLANEOUS
	19B216176G1	Harness (Encoder/Decoder), Includes:
P314	4029840P2	Contact, electrical; sim to Amp 42827-2.
P318	4029840P2	Contact, electrical; sim to Amp 42827-2.
P321	4029840P2	Contact, electrical; sim to Amp 42827-2.
P328 thru P335	4029840P2	Contact, electrical; sim to Amp 42827-2.

	SYMBOL	GE PART NO.	DESCRIPTION
			CHANNEL GUARD MODIFICATION KIT 19A127178G2 (Used with A402)
			MISCELLANEOUS
١		19B216177Gl	Harness (Tone Reject Filter). Includes:
-	P321	4029840P2	Contact, electrical; sim to Amp 42827-2.
	P330	4029840P2	Contact, electrical; sim to Amp 42827-2.
	P332	4029840P2	Contact, electrical; sim to Amp 42827-2.
			MECHANICAL PARTS (SEE RC-1692)
	1	19B204583G3	Hinge.
	2	19B216727P1	Support. (Used with Q341 and Q342).
	3	19A116023P2	Plate, insulated. (Used with Q341 and Q342).
	4	19A116022P1	Insulator. (Used with Q341 and Q342).
	5	4029851P6	Clip, loop.
	6	19B204583G1	Hinge.
	7	19B204583G2	Hinge.
	8	19A121676P1	Guide pin.
	9	19C3O3396G4	Bottom cover. (Station)
,	10	19C3O3385G1	Bottom cover. (Mobile)
	11	19A121297P1	Angle.
	12	7160861 P4	Nut. (Used to secure cover).
	13	4036555Pl	Insulator disc. (Used with Q7 on A348).
	14	4035267P2	Button, plug. (Used with A348, A350 and A402).
	15	19C3O3495G3	Top cover. (Station, except Repeaters and VM).
	16	19C303676G2	Top cover. (Station, Repeaters and VM only).
	17	19C303385P2	Top cover. (Mobile)
ı	18	4029851P3	Clip, loop.
l	19	19A121383P1	Support,
	20	4033089Pl	Clip. (Part of XY1-XY4).
ı	21	19B200525P9	Rivet. (Part of XY1-XY4).
	22	19A115793P1	Contact. (Part of XY1-XY4).
	23	4039307P1	Crystal socket. (Part of XY1-XY4).
	24	19C303541P1	Cover.
	25	19C317344P3	Heat sink.
	26	19C303389G1	Chassis.
	27	4034252P5	Can (Used with Tl on A347).
	28	19B204672P1	Cover.
	29	7162414P1	Retainer, transistor. (Used with Ql on A341).
ı	30	19B204917P1	Support.



PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - 2nd Mixer A347 (19B216119-G1)

To make receivers compatible with solid-state transmitters. Added C17.

REV. A - Blanker A370-A372 (Part of 19E500873-G4 thru -G6)

To improve blanking of high repetition rate noise. Changed C23.

REV. B - Level Shut-Off Switch A376 and Blanker A370-A372 (Part of 19E500873-G4 thru -G6)

To improve receiver selectivity. Changed C5 and C6, and added R11 and R12 in A376. Replaced jumper from H2 to H5 with R26 on A370-A372.

Schematic Diagram Was:

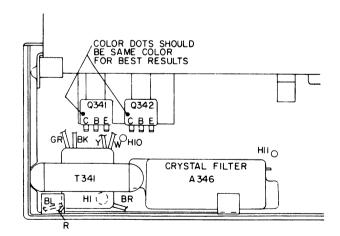
REV. C - 19E500873-G4 thru -G6 (Chassis & RF Assembly)

To protect the receiver against positive voltage transients. Added thyrector CR1 between J443-11 and J443-13.

REV. D - $\underline{19E500873-G4}$ thru -G6 (Chassis & RF Assembly)

To incorporate new PA transistors. Changed Q341 and Q342 and added R346.

Outline Diagram Was:



PRODUCTION CHANGES

25—50 MHz MASTR RECEIVER MODELS 4ER39C10-27

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Issue 3

- REV. C 1st Osc/Mult A352 & A353
- REV. A 1st Osc/Mult A354 thru A357

These revisions incorporated into initial shipment.

REV. A - Channel Guard Encoder/Decoder Model 4EK16A10

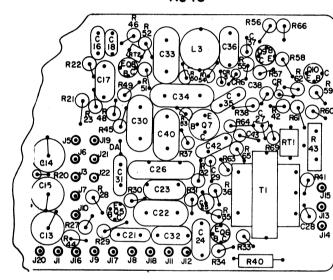
To obtain correct output level. Changed R8.

REV. A - IF Audio & Squelch Board A348 (19D413129-G1)

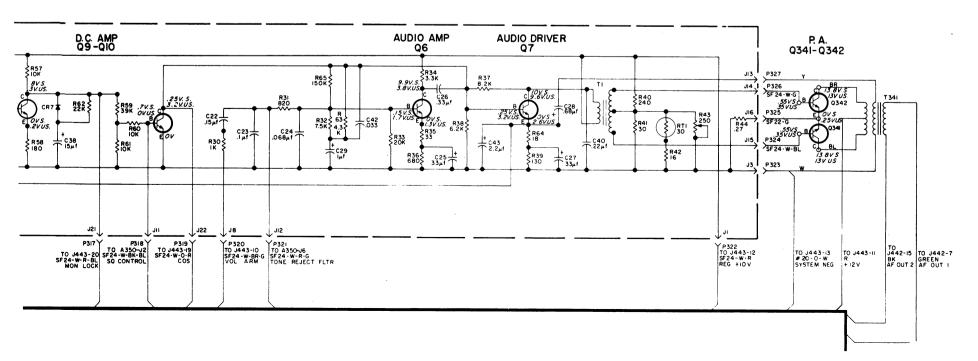
To make IF Audio & Squelch Board compatible with new PA transistors and to improve squelch operation. Added C49-C54, CR8, R75-R79, and RT3. Deleted C24, C28, C29, C42, C43, R32, R37, R63 and R65. Changed C21, C26, C37, C38, C40 R33, R38, R39, R41, R42, R48, R53 and R62.

Outline Diagram Was:

IF-AUDIO & SQUELCH BOARD A348



Schematic Diagram Was:



CHASSIS AND RF ASSEMBLY 19E500873G4 THRU G6

Rev. E - To eliminate squelch opening thump in receivers with Channel Guard. Removed white-orange wire between J443-13 and TB2-1.

Added a white-orange wire between P312 (or J17 on IF Audio and Squelch board) and TB2-1.

IF AUDIO AND SQUELCH BOARD A348 (19D413129G1)

Rev. B - To control more closely the squelch control rotation. Changed R48.

Rev. C - To eliminate barely audible squelch switching transients and to reduce receiver squelch tail.

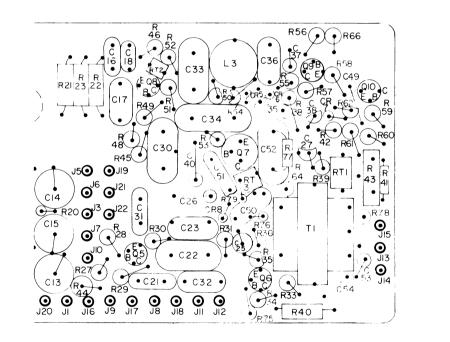
DELETED C38, C49, CR7, CR8, R62, R75 and R76

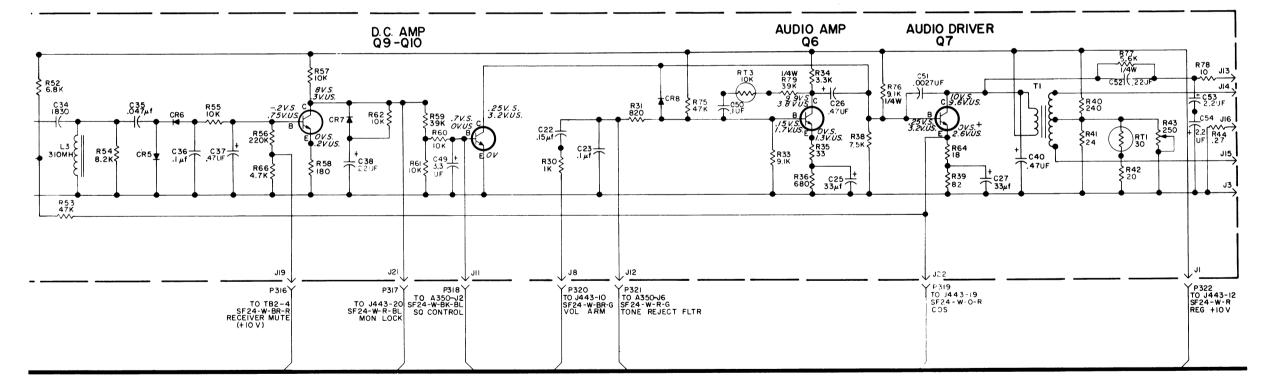
ADDED C55, R80, R81 and R82

CHANGED C27, C36, R53, R64 and R77

Outline Diagram Was:

Schematic Diagram Was:





PRODUCTION CHANGES

25-50 MHZ MASTR RECEIVER MODELS 4ER39C10-27

ADDENDUM TO LBI-3925B (25-50 MHz Receiver Models 4ER39C28-45)

The following revision letter changes have been made to improve receiver performance and to facilitate production. The revision stamped on the assemblies includes all previous revisions.

CHASSIS AND RF ASSEMBLY 19E500873-G4 THRU G6

Rev. E - To eliminate squelch opening thump in receivers with Channel Guard. Removed white-orange wire between J443-13 and TB2-1. Added a white-orange wire between P312 (or J17 on IF Audio and Squelch board) and TB2-1.

IF AUDIO & SQUELCH BOARD A348 (19D413129-G1)

Rev. B - To control more closely the squelch control rotation. Changed R48 from 3R77-P332J (3300 ohms $\pm 5\%$) to 19A116278-P249 (3160 ohms $\pm 2\%$).

Rev. C - To eliminate barely audible squelch switching transients and to reduce reciever squelch tail.

DELETED: C38, C49, CR7, CR8, R62, R75 and R76

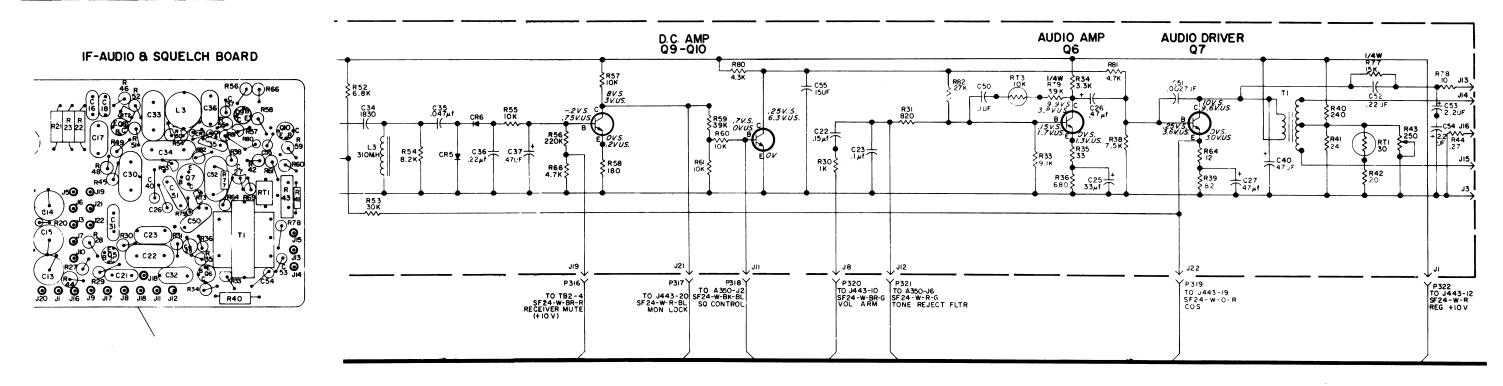
ADDED: C55 (5496267-P14, 15 μ F)

R80 (3R152-P432J, 4.3K ohms ±5%) R81 (3R152-P472J, 4.7K ohms ±5%) R82 (3R77-P273J, 27K ohms ±5%)

CHANGED	FROM	TO
C27	5496267-P6 (33 μ F)	5496267-P2 (47 μF)
C36	19B209243-P7 (0.1 μF)	19B209243-P17 (0.22 μF)
R53	3R77-P473J (47K ohms)	3R77-P303J (30K ohms)
R64	3R77-P180J (18 ohms)	3R77-P120J (12 ohms)
R 77	3R152-P562J (5.6K ohms)	3R152-P153J (15K ohms)

Outline Diagram Changed To:

Schematic Diagram Changed To:



ORDERING SERVICE PARTS

Each component appearing on the schematic diagram is identified by a symbol number, to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part Number.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- 1. GE Part Number for component
- 2. Description of part
- 3. Model number of equipment
- 4. Revision letter stamped on unit

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

Should further information be desired, or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

LBI-3925

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MOBILE RADIO DEPARTMENT LYNCHBURG, VIRGINIA 24502

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